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Human &Digital

2001 MEMORY

hynix

Hynix Semiconductor has always pursued the world's industry leader through aggressive R&D investment, continuous innovation, and total customer satisfaction...

Hynix Semiconductor Inc. is redefining and reshaping itself in response to the rapidly changing market.
The company is transforming into a flexible and streamlined organization that actively pursues technological innovation to enhance the quality of life for all.



Index

New SDRAM PART NUMBERING

HY XX X XX XX X X XX X X - XX X

HYNIX MEMORY

PRODUCT GROUP
57 : SDRAM

PROCESS & POWER SUPPLY
V : CMOS, 3.3V

DENSITY & REFRESH
64 : 64M, 4K Refresh
65 : 64M, 8K Refresh
28 : 128M, 4K Refresh
56 : 256M, 8K Refresh

ORGANIZATION
4 : x4
8 : x8
16 : x16
32 : x32

BANK
1 : 2Bank
2 : 4Bank

INTERFACE
0 : LVTTL
1 : SSTL_3

DIE GENERATION

Ichon		Cheong-ju
BLANK	1st Gen.	H : 1st Gen.
A	2nd Gen.	HA : 2nd Gen.
B	3rd Gen.	HB : 3rd Gen.
C	4th Gen.	HC : 4th Gen.

POWER CONSUMPTION
BLANK : Normal Power
L : Low Power

PACKAGE
T : TSOP
Q : TQFP
F : FBGA
L : CSP (LF-CSP)
S : Stacked (A-Type)
K : Stacked (B-Type)

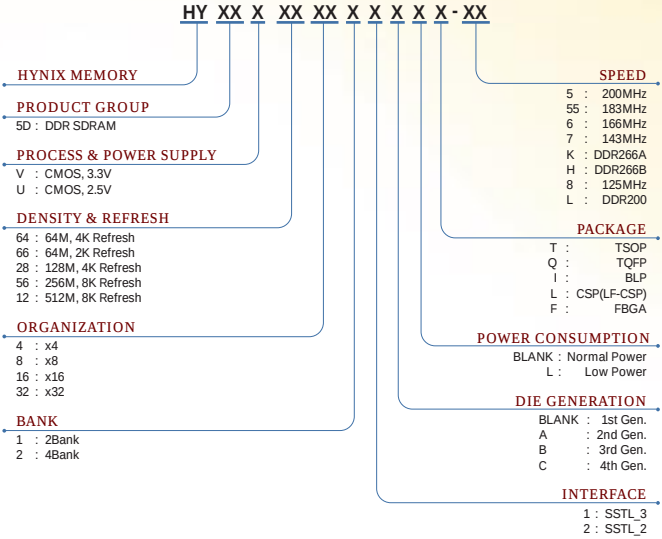
SPEED
5 : 200MHz
55 : 183MHz
6 : 166MHz
7 : 143MHz
K : PC133,CL2
H : PC133,CL3
8 : 125MHz
P : PC100, CL2
S : PC100, CL3
10 : 100MHz

TEMPERATURE
I : Industrial Temperature
E : Extended Temperature

Applicable Part List (Examples of x4 Model)

64M	G	HY57V64420HGT (Cheong-ju)
128M	3rd	HY57V28420AT (Ichon)
	C	HY57V28420HCT (Cheong-ju)
256M	1st	HY57V56420T (Ichon)
	2nd	HY57V56420AT (Ichon)

New DDR SDRAM PART NUMBERING



New Part Numbering system after merger

New D-RDRAM PART NUMBERING

HY XX X XXX XX X X XX

HYNIX MEMORY

PRODUCT GROUP

5R : D-RDRAM

PROCESS & POWER SUPPLY

NONE : CMOS, 2.5V
W : CMOS, 1.8V

DENSITY & REFRESH

64/72 : 64/72M, 8K Refresh
128/144 : 128/144M, 8K Refresh
256/288 : 256/288M, 8K Refresh

SPEED*

40 : 40ns
45 : 45ns
50 : 50ns
53 : 53ns

I/O FREQUENCY

6 : 600MHz
7 : 711MHz
8 : 800MHz

PACKAGE

E : Edge Bonding
C : Center Bonding
M : Mirror

DIE GENERATION

Ichon		Cheong-ju	
BLANK	: 1st Gen.	H	: 1st Gen.
A	: 2nd Gen.	HA	: 2nd Gen.
B	: 3rd Gen.	HB	: 3rd Gen.
C	: 4th Gen.	HC	: 4th Gen.

NOTE) SPEED*=tRAC : Row Access Time

New Part Numbering system after merger

New FP/EDO DRAM PART NUMBERING

HY XX X(X) X XX X X XX X X - XX

HYNIX MEMORY

PRODUCT GROUP

51 : FP/EDO DRAM

PROCESS & POWER SUPPLY

V : CMOS, 3.3V
VL : CMOS, 2.35V

REFRESH

BLANK : Standard
S : Self Refresh

DENSITY & REFRESH

16 : 16M, 4K Refresh
17 : 16M, 2K Refresh
18 : 16M, 1K Refresh
64 : 64M, 8K Refresh
65 : 64M, 4K Refresh

ORGANIZATION

40 : x4
41 : x4 (4CAS)
80 : x8
16 : x16
17 : x16 (2CAS)
18 : x16 (2WE)
32 : x32 (2CAS)
33 : x32 (2WE)
34 : x32 (4CAS)

SPEED

45 : 45ns
5 : 50ns
6 : 60ns
7 : 70ns
8 : 80ns
10 : 100ns
(in case of 2.35V)

PACKAGE

J : SOJ
T : TSOP
R : TSOP(REVERSE)
I : BLP

POWER CONSUMPTION

BLANK : Normal Power
L : Low power
SL : Self Refresh with Low Power

DIE GENERATION

Ichon		Cheong-ju	
BLANK	: 1st Gen.	H	: 1st Gen.
A	: 2nd Gen.	HA	: 2nd Gen.
B	: 3rd Gen.	HB	: 3rd Gen.
C	: 4th Gen.	HC	: 4th Gen.

ACCESS MODE

0 : FP Mode
3 : EDO Mode

New Part Numbering system after merger

New SDRAM MODULE PART NUMBERING

HYM XX X XX X X X XX X X X X - X

HYNIX MODULE

COMPONENT GROUP

76 : 64Mb SDRAM
71 : 128Mb SDRAM
72 : 256Mb SDRAM
75 : 512Mb SDRAM
7G : 1Gb SDRAM

POWER SUPPLY & INTERFACE

V : CMOS , 3.3V , LVTTL
S : SSTL_3

MEMORY DEPTH

4 : 4M
8 : 8M
32 : 32M
12 : 128M
16 : 16M
64 : 64M
51 : 512M

MODULE TYPE

NONE : 168pin Unbuffered DIMM
R : JEDEC 168pin Registered DIMM W/PLL
E : INTEL 168pin Registered DIMM W/O PLL
S : INTEL 168pin Registered DIMM W/PLL
C : RCC 168pin Registered DIMM W/PLL
D : JEDEC 200pin Registered DIMM W/PLL
M : 144pin SODIMM
W : SUN 232pin Registered DIMM W/PLL

DATA WIDTH

64/72 : x64/x72
65/75 : x64/x72 (PC100)
63/73 : x64/x72 (PC133)
145 : x144 (PC100)
143 : x144 (PC133)

SPEED

K : PC133 CL2
H : PC133 CL3
P : PC100 CL2
S : PC100 CL3

MODULE REVISION

NONE : Original
M : 1st Rev. N : 2nd Rev.

COMPONENT CONFIGURATION

4 : x4 Based
8 : x8 Based
6 : x16 Based

PACKAGE

T : TSOP
K : Stack (B Type)
J : Stack (C Type)
TU : TSOP + Micro SODIMM
S : Stack (A Type)

POWER CONSUMPTION

NONE : Normal Power
L : Low Power

DIE GENERATION

Ichon		Cheong-ju	
NONE :	1st Generation	H :	1st Generation
A :	2nd Generation	HA :	2nd Generation
B :	3rd Generation	HB :	3rd Generation
C :	4th Generation	HC :	4th Generation

REFRESH / INTERNAL BANK

1 : 4K Ref. / 2Bank
2 : 8K Ref. / 2Bank
3 : 16K Ref. / 2Bank
5 : 4K Ref. / 4Bank
6 : 8K Ref. / 4Bank
7 : 16K Ref. / 4Bank

New Part Numbering system after merger

New DDR SDRAM MODULE PART NUMBERING

HYM XX X XX X X X XX X X X X - X

HYNIX MODULE

COMPONENT GROUP

D1 : 128Mb DDR SDRAM
D2 : 256Mb DDR SDRAM
D5 : 512Mb DDR SDRAM
DG : 1Gb DDR SDRAM

POWER SUPPLY & INTERFACE

NONE : CMOS, 2.5V, SSTL_2

MEMORY DEPTH

8 : 8M
16 : 16M
32 : 32M
64 : 64M
12 : 128M
51 : 512M
1G : 1G

MODULE TYPE

NONE : 184pin Unbuffered DIMM
G : 184pin Registered DIMM
M : 200pin SODIMM
R : 200pin Registered DIMM

DATA WIDTH

64 : x64
72 : x72

SPEED

K : DDR266A
H : DDR266B
L : DDR200

MODULE REVISION

NONE : Original
M : 1st Rev.
N : 2nd Rev.

COMPONENT CONFIGURATION

4 : x4 Based
8 : x8 Based
6 : x16 Based

PACKAGE

NONE : Normal TSOP
Q : TQFP
S : Stack (A Type)
K : Stack (B Type)

POWER CONSUMPTION

NONE : Normal Power
L : Low Power

DIE GENERATION

NONE : 1st Gen.
A : 2nd Gen.
B : 3rd Gen.
C : 4th Gen.

REFRESH / INTERNAL BANK

1 : 4K Ref. / 2Bank
2 : 8K Ref. / 2Bank
3 : 16K Ref. / 2Bank
5 : 4K Ref. / 4Bank
6 : 8K Ref. / 4Bank
7 : 16K Ref./ 4Bank

New Part Numbering system after merger

New D-RDRAM MODULE PART NUMBERING

HYM XX X XXX X XX X X X - XX

HYNIX MODULE

COMPONENT GROUP

R1 : 128/144Mb D-RDRAM
R2 : 256/288Mb D-RDRAM
R5 : 512/576Mb D-RDRAM

POWER SUPPLY & INTERFACE

NONE : CMOS, 2.5V
W : CMOS, 1.8V

MEMORY DEPTH

32 : 32M
48 : 48M
64 : 64M
96 : 96M
128 : 128M
256 : 256M

MODULE TYPE

NONE : 184pin RIMM
M : SORIMM

SPEED*

40 : 40ns
45 : 45ns
50 : 50ns
53 : 53ns

I/O FREQUENCY

6 : 600MHz
7 : 711MHz
8 : 800MHz

MODULE REVISION

NONE : Original
M : 1st Rev.
N : 2nd Rev.

DIE GENERATION

	Ichon		Cheong-ju
BLANK	: 1st Gen.	H	: 1st Gen.
A	: 2nd Gen.	HA	: 2nd Gen.
B	: 3rd Gen.	HB	: 3rd Gen.
C	: 4th Gen.	HC	: 4th Gen.

DATA WIDTH

16 : x16(Non ECC)
18 : x18(ECC)

NOTE) SPEED*=tRAC : Row Access Time

New Part Numbering system after merger

New DRAM MODULE PART NUMBERING

HYM XX X XX XX X X X X X X X - XX

HYNIX MODULE

COMPONENT GROUP

A1 : 16Mb Async. DRAM
A6 : 64Mb Async. DRAM

POWER SUPPLY & INTERFACE

None : 5.0V(TTL)
V : 3.3V(LVTTL)

MEMORY DEPTH

1	: 1M	8	: 8M
2	: 2M	16	: 16M
4	: 4M	32	: 32M

DATA WIDTH

8 / 9	: x8/x9	64	: x64
32	: x32	65	: x64 (2CAS)
33	: x32(2CAS)	66	: x64 (2WE)
34	: x32(2WE)	67	: x64 (4CAS)
36	: x36	72	: x72
37	: x36, ECC	73	: x72, ECC
40	: x40, ECC	14	: x144

REFRESH

0	: 4K Refresh	2	: 1K Refresh
1	: 2K Refresh	3	: 8K Refresh

DRAM OPERATION MODE

F : Fast page mode
E : EDO Mode

SPEED

45 : 45ns
5 : 50ns
6 : 60ns
7 : 70ns

PACKAGE TYPE

S :	SOJ, Solder	SG :	SOJ, Gold
T :	TSOP, Solder	TG :	TSOP, Gold
I :	BLP, Solder	IG :	BLP, Gold

MODULE REVISION

None : Original
M : 1st Rev. N : 2nd Rev.
H : Height(1.5inch only)

DIE GENERATION

Ichon		Cheong-ju	
None	: 1st Gen.	H	: 1st Gen.
A	: 2nd Gen.	HA	: 2nd Gen.
B	: 3rd Gen.	HB	: 3rd Gen.
C	: 4th Gen.	HC	: 4th Gen.

COMPONENT CONFIGURATION

4 : x4 Based, 8 : x8 Based, 6 : x16 Based

MODULE TYPE

0 : 72pin SIMM
1 : 168pin Buffered DIMM
2 : 200pin Buffered DIMM
3 : 168pin Unbuffered DIMM
4 : 144pin SO-DIMM

New SLOW SRAM PART NUMBERING

HY XX X X XX XX X X - X X XX X

HYNIX MEMORY

PRODUCT GROUP
62 : Slow SRAM

POWER SUPPLY
C : 5.0V , V : 3.3V
U : 3.0V , Q : 2.5V , S : 1.8V
K : 2.7V~3.6V, W : 2.7V~5.5V

TECH. + CLASSIFICATION
L : HLR
T : TFT
F : Full CMOS

BIT ORGANIZATION
08 : x8 , 16 : x16
32 : x32 , 64 : x64

DENSITY
08 : 256K, 10 : 1M, 20 : 2M
40 : 4M, 80 : 8M, 16 : 16M

MODE
1 : 1CS
2 : 2CS
3 : 1CS with /UB,/LB ; tOE
4 : 1CS with /UB,/LB ; tCS
5 : 2CS with /UB,/LB ; tOE
6 : 2CS with /UB,/LB ; tCS
7 : I/O Control with Byte
8 : Customer Option
9 : MUX Address

DIE GENERATION
M : 1st Generation
A : 2nd Generation
B : 3rd Generation
C : 4th Generation

TEMPERATURE
C : 0°C ~ 70°C
E : - 25°C ~ 85°C
I : - 40°C ~ 85°C

SPEED
55 : 55ns
70 : 70ns
85 : 85ns
10 : 100ns

PACKAGE
P : PDIP
G : SOP
M : uBGA
F : FBGA
T : TSOP- I
S : Small TSOP- I
D : TSOP- II
R : TSOP- I (Reversed)
U : Small TSOP- I (Reversed)
V : TSOP- II (Reversed)
W : Wafer
C : Chip

POWER CONSUMPTION
N : Standard
L : Low Power
D : Low Low Power
S : Super Low Power

New Part Numbering system after merger

FLASH PART NUMBERING (Ichon)

HY XX XXX XXX X X X - XX X

HYNIX MEMORY

PRODUCT GROUP

29 : Flash Memory

POWER SUPPLY & MODE

F : 5.0V
LV : 3.0V
DL : 3.0V Dual Bank
DS : 2.0V Dual Bank
BDS : 2.0V Burst Mode, Dual Bank

DENSITY

002* : 2M(x8)

400 : 4M(x8/x16),	040 : 4M(x8),	004* : 4M(x8)
800 : 8M(x8/x16),	080 : 8M(x8),	008* : 8M(x8)
160 : 16M(x8/x16),	162 : 16M(x8/x16),	163 : 16M(x8/x16)
320 : 32M(x8/x16),	322 : 32M(x8/x16),	323 : 32M(x8/x16)

* : x8 organization with boot code sector architecture

DIE GENERATION

BLANK : 1st Generation
A : 2nd Generation
B : 3rd Generation

TEMPERATURE

BLANK : Commercial (0°C~70°C)
I : Industrial (-40°C~85°C)
E : Extended (-55°C~125°C)

SPEED

45 : 45ns
55 : 55ns
70 : 70ns
85 : 85ns
90 : 90ns
12 : 120ns

PACKAGE

T : Standard TSOP
R : Reversed TSOP
C : PLCC
G : PSOP
P : PDIP
F : FBGA

SECTOR ARCHITECTURE

BLANK : Uniform Sector
T : Top Sector
B : Bottom Sector

Old Part Numbering system before merger

DRAM PART NUMBERING (Ichon)

HY 51 X XX XXX X X - XX XX X

HYNIX I-Site
Memory Product

PRODUCT GROUP
51 : DRAM

PROCESS & POWER SUPPLY
BLANK : CMOS, 5.0V
V : CMOS, 3.3V

DENSITY & REFRESH
2 : 2M
4 : 4M
16 : 16M, 4K Refresh
17 : 16M, 2K Refresh
18 : 16M, 1K Refresh
64 : 64M, 8K Refresh
65 : 64M, 4K Refresh

DATA WIDTH & FEATURES
100 : x1(FP)
400 : x4(FP)
404 : x4(EDO)
407 : x4(EDO, 4CAS)
800 : x8(FP)
804 : x8(EDO)
160 : x16(FP)
164 : x16(EDO)
260 : x16(FP) @ 2/4Mb
264 : x16(EDO) @ 2/4Mb

DIE GENERATION
BLANK : 1st Generation
A : 2nd Generation
B : 3rd Generation
C : 4th Generation

POWER CONSUMPTION
BLANK : Normal Power
L : Low Power
SL : Self Refresh with Low Power

PACKAGE
J : 300mil SOJ
JC : 400mil SOJ
T : 300mil TSOPII
TC : 400mil TSOPII

SPEED
45 : 45ns
50 : 50ns
60 : 60ns
70 : 70ns

I : Industrial Temperature
E : Extended Temperature

Old Part Numbering system before merger

SDRAM PART NUMBERING (Ichon)

HY XX X XXX XX X X X XX XX - XXX X

HYNIX I-Site
Memory Product

PRODUCT GROUP
57 : SDRAM
5D : DDR SDRAM

PROCESS & POWER SUPPLY
V : CMOS, 3.3V
U : CMOS, 2.5V

DENSITY & REFRESH
4 : 4M, 1K Refresh
16 : 16M, 4K Refresh
64 : 64M, 8K Refresh
65 : 64M, 4K Refresh
129 : 128M, 4K Refresh
257 : 256M, 8K Refresh

DATA WIDTH
40 : x4
80 : x8
16 : x16
32 : x32

BANK
1 : 2Bank
2 : 4Bank

I : Industrial Temperature
E : Extended Temperature

SPEED*
5 : 5ns(200MHz)
55 : 5.5ns(183MHz)
6 : 6ns(166MHz)
7 : 7ns(143MHz)
75 : 7.5ns (133MHz)
8 : 8ns (125MHz)
10P : 10ns (100MHz) CL2&3
10S : 10ns (100MHz) CL3
10 : 10ns (100MHz)
12 : 12ns (83MHz)
15 : 15ns (66MHz)

PACKAGE
TC : 400mil TSOPII
TQ : 100Pin- TQFP

POWER CONSUMPTION
BLANK : Normal Power
L : Low Power

DIE GENERATION
BLANK : 1st Generation
A : 2nd Generation
B : 3rd Generation
C : 4th Generation
D : 5th Generation

INTERFACE
0 : LVTTL
1 : SSTL
2 : SSTL_2

* Note : 10P / 10S - PC100 Compliant
10 - PC66 Compliant

Old Part Numbering system before merger

DRAM MODULE PART NUMBERING (Ichon)

HYM X X XX X XX X X X X X X X - XX

HYNIX I-Site
Memory Module

FAMILY
5 : DRAM

OPERATION VOLTAGE
NONE : 5.0V (TTL)
V : 3.3V (LVTTL)

DATA WIDTH
8/9 : x8/x9
32/36/39/40/48 : x32/x36/x39/x40/x48
64/72 : x64/x72
144 : x144

BYTE / ECC ACCESS
NONE : BYTE
A : ECC

DEPTH
1 : 1M
2 : 2M
4 : 4M
8 : 8M
16 : 16M
32 : 32M

REFRESH
0 : 4K Refresh
1 : 2K Refresh
2 : 1K Refresh
3 : 8K Refresh

DRAM OPERATION MODE
0 : Fast Page Mode
4 : EDO Mode

SPEED
6 : 60ns
7 : 70ns
8 : 80ns

MODULE INDEX
NONE, 1, 2, 3 · · · : Index number to distinguish modules using different PCB or sub-materials with same module configuration and operation

PLATE TYPE
NONE : Tin
G : Gold

CONNECTOR TYPE
M : x4 Based SIMM
E : x8 Based SIMM
W : x16 Based SIMM
K : x4 Based Unbuffered DIMM
F : x8 Based Unbuffered DIMM
R : x16 Based Unbuffered DIMM
N : x4 Based Buffered DIMM
H : x8 Based Buffered DIMM
X : x16 Based Buffered DIMM
P : x4 Based SODIMM
Z : x8 Based SODIMM
Q : x16 Based SODIMM

COMPONENT PACKAGE TYPE
NONE : SOJ
T : TSOP

POWER CONSUMPTION
NONE : Normal Power
L : Low Power
SL : Self Refresh with Low Power

MODULE GENERATION
NONE : 1st Generation
A : 2nd Generation
B : 3rd Generation
C : 4th Generation
D : 5th Generation

Old Part Numbering system before merger

SDRAM MODULE PART NUMBERING (Ichon)

16/64Mb SDRAM Based

HYM X X XX X X X(X) X X X X X X X - X(X)(X)

HYNIX I-Site
Memory Module

PRODUCT GROUP
7 : 16/64Mb SDRAM

POWER SUPPLY & INTERFACE
V : 3.3V, LVTTL
S : 3.3V, SSTL

DATA WIDTH
64/72 : x64/x72 (PC66)
65/75 : x64/x72 (PC100)
63/73 : x64/x72 (PC133)

ERROR DETECTION SCHEME
NONE : NONE or PARITY
A : ECC

DIMM TYPE
NONE : 168pin Unbuffered DIMM
E : 168pin Registered DIMM w/o PLL (Intel)
S : 168pin Registered DIMM w/ PLL (Intel)
R : 168pin Registered DIMM (JEDEC)
C : 168pin Registered DIMM (RCC)
D : 200pin Registered DIMM (JEDEC)

MEMORY DEPTH
1 : 1M
2 : 2M
4 : 4M
8 : 8M
16 : 16M

REFRESH
0 : 4K Refresh
1 : 2K Refresh
2 : 1K Refresh
3 : 8K Refresh

SPEED
75 : 7.5ns (133MHz)
8 : 8ns (125MHz)
10P : 10ns (PC100) CL2&3
10S : 10ns (PC100) CL3
10 : 10ns (100MHz)

MODULE INDEX
NONE, 1, 2, 3 ... : Index # to distinguish Using different PCB or sub-material with same module config. & operation

PLATING
G : Gold

COMPONENT DATA WIDTH & DIMM TYPE
K : x4 Based Unbuffered DIMM
F : x8 Based Unbuffered DIMM
R : x16 Based Unbuffered DIMM
N : x4 Based 168pin Registered DIMM
H : x4 Based 168pin Registered DIMM
X : x8 Based 168pin Registered DIMM
P : x4 Based SODIMM
Q : x16 Based SODIMM
Z : x8 Based SODIMM

COMPONENT PACKAGE TYPE
T : 400mil TSOPII

POWER CONSUMPTION
NONE : Normal Power
L : Low Power

COMPONENT GENERATION
NONE : 1st Generation
A : 2nd Generation
B : 3rd Generation
C : 4th Generation
D : 5th Generation

COMPONENT INTERNAL BANK
0 : Using 2 Banks SDRAM
1 : Using 4 Banks SDRAM

Old Part Numbering system before merger

SDRAM MODULE PART NUMBERING (Ichon)

128/256Mb Based

HYM XX X XX X X X X X X X X - XXX

HYNIX I-Site
Memory Module

COMPONENT GROUP
71 : 128Mb SDRAM
72 : 256Mb SDRAM
75 : 512Mb SDRAM
7G : 1Gb SDRAM

POWER SUPPLY & INTERFACE
V : 3.3V, LVTTL
S : 3.3V, SSTL

DATA WIDTH
64/72 : x64/x72 (PC66)
65/75 : x64/x72 (PC100)
63/73 : x64/x72 (PC133)

DIMM TYPE
NONE : 168pin Unbuffered DIMM
R : JEDEC Type 168pin Registered DIMM w/PLL
E : INTEL Type 168pin Registered DIMM w/o PLL
S : INTEL Type 168pin Registered DIMM w/PLL
C : RCC Type 168pin Registered DIMM w/pll
D : JEDEC Type 200pin Registered DIMM w/PLL
M : 144pin SODIMM

MEMORY DEPTH
8 : 8M
16 : 16M
28 : 128M
32 : 32M
64 : 64M
12 : 512M

REFRESH
0 : 4K Refresh
1 : 2K Refresh
2 : 1K Refresh
3 : 8K Refresh

SPEED
75 : 7.5ns (133MHz)
8 : 8ns (125MHz)
10P : 10ns (PC100) CL2&3
10S : 10ns (PC100) CL3
10 : 10ns (100MHz)

CONNECTOR TYPE
N : x4 Based
H : x8 Based
X : x16 Based
HX : x8/x16 Based
XH : x16/x8 Based (1 Bank/2Bank)

COMPONENT PACKAGE
NONE : SOJ
T : TSOP
S : Stacked pkg (A type)
K : Stacked pkg (B type)

POWER CONSUMPTION
NONE : Normal Power
L : Low Power

COMPONENT GENERATION
NONE : 1st Generation
A : 2nd Generation
B : 3rd Generation
C : 4th Generation
D : 5th Generation

COMPONENT INTERNAL BANK
0 : Using 2 Banks SDRAM
1 : Using 4 Banks SDRAM

* Note : 10P part meets tAC=6ns at both CAS Latency 2 and 3
10S part only meets tAC=6ns at CAS Latency 3

Old Part Numbering system before merger

DRAM PART NUMBERING (Cheong Ju)

16M DRAM

GM 71 X X XX XX X X X X - XX

HYNIX C-Site
Memory Product

FAMILY
71 : DRAM

PROCESS
C : CMOS (5V)
V : CMOS (3.3V)
VL : CMOS(2.35V)

REFRESH
BLANK : Standard
S : Self Refresh

DENSITY & REFRESH CYCLE
16 : 16M, 4K Refresh
17 : 16M, 2K Refresh
18 : 16M, 1K Refresh

ORGANIZATION
10 : x 1
40 : x 4
41 : x 4, 4CAS
80 : x 8
16 : x 16

ACCESS MODE
0 : Fast Page Mode
3 : EDO Mode

SPEED
5 : 50ns
6 : 60ns
7 : 70ns
8 : 80ns
1 : 100ns
(in case of Vcc=2.35V)

PACKAGE
J : SOJ
T : TSOP(Normal)
R : TSOP(Reverse)
I : BLP

POWER CONSUMPTION
BLANK : Standard
L : Low-Power

REVISION NO.
BLANK : Original
A : First
B : Second
C : Third

Old Part Numbering system before merger

DRAM PART NUMBERING (Cheong Ju)

64M DRAM

GM 71 X X XX XX X X X X - XX

HYNIX C-Site
Memory Product

FAMILY
71 : DRAM

PROCESS
C : CMOS (5V)
V : CMOS (3.3V)

REFRESH
BLANK : Standard
S : Self Refresh

DENSITY & REFRESH CYCLE
64 : 64M, 8K Refresh
65 : 64M, 4K Refresh

ORGANIZATION & CONTROL MODE
10 : x 1
40 : x 4
80 : x 8
16 : x 16(2CAS)
17 : x 16(2WE)
32 : x 32(2CAS)
33 : x 32(2WE)
34 : x 32(4CAS)

ACCESS MODE
0 : Fast Page Mode
3 : EDO Mode

SPEED
5 : 50ns
6 : 60ns
7 : 70ns
8 : 80ns

PACKAGE
BLANK : Plastic DIP
J : SOJ
T : TSOP(Normal)
R : TSOP(Reverse)
I : BLP

POWER CONSUMPTION
BLANK : Standard
L : Low-Power

REVISION NO
BLANK : Original
A : First
B : Second
C : Third

SDRAM PART NUMBERING (Cheong Ju)

GM 72 X XX XX X X X X X - XXX

HYNIX C-Site
Memory Product

PRODUCT GROUP
SDRAM

PROCESS & POWER SUPPLY
V : CMOS, 3.3V

DENSITY & REFRESH
16 : 16M, 4K Refresh
17 : 16M, 2K Refresh
28 : 128M, 4K Refresh
64 : 64M, 16K Refresh
65 : 64M, 8K Refresh
66 : 64M, 4K Refresh

ORGANIZATION
4 : x4
8 : x8
16 : x16
32 : x32

BANK
1 : 1Bank
2 : 2Bank
4 : 4Bank
8 : 8Bank

INTERFACE
1 : LVTTL

SPEED
6 : 166MHz
65 : 153MHz
7 : 143MHz
75 : 133MHz
8 : 125MHz
7K : PC100, 2-2-2^
7J : PC100, 3-2-2^^
10K : PC66 *
10J : PC66 **
12 : 83MHz
15 : 66MHz

PACKAGE
T : TSOP(Normal)
R : TSOP(Reverse)
I : BLP
S : Stack

POWER CONSUMPTION
BLANK : Normal Power
L : Low Power

REVISION NO.
BLANK : Original
A : First
B : Second
C : Third
D : Fourth
E : Fifth
F : Sixth

Note) ^ 7K means to meet tCK=10ns, CL=2, tAC=6ns
^^ 7J means to meet tCK=10ns, CL=3, tAC=6ns
* 10K means to meet tCK=15ns, CL=2, tAC=9ns
** 10J means to meet tCK=10ns, CL=3, tAC=9.5ns

Old Part Numbering system before merger

DRAM MODULE PART NUMBERING (Cheong Ju)

16MD Based

GMM X 7 XX XX X X X X X XX - XX

HYNIX C-Site
Memory Module

MANUFACTURE
BLANK : LGS
S : Smart
T : Tanisys

FAMILY
7 : DRAM

ORGANIZATION
8 : x8
9 : x9
32 : x32
36 : x36
37 : x36, ECC
40 : x40, ECC
64 : x64
72 : x72
73 : x72, ECC
14 : x144

DEPTH
1 : 1M
2 : 2M
4 : 4M
8 : 8M
16 : 16M

REFRESH
0 : 1K Refresh
1 : 2K Refresh
2 : 4K Refresh
3 : 8K Refresh

ACCESS / VOLTAGE MODE
5 : Fast Page Mode, 5V
6 : EDO Mode, 5V
7 : Fast Page Mode, 3.3V
8 : EDO Mode, 3.3V

SPEED
6 : 60ns
7 : 70ns
8 : 80ns

PACKAGE & TERMINAL
S : SOJ, Solder
SG : SOJ, Gold
T : TSOP, Solder
TG : TSOP, Gold
I : BLP, Solder
IG : BLP, Gold

MDL REVISION NO.
BLANK : Original
N : First
M : Second
L : Third

IC REVISION NO.
BLANK : Original
A : First
B : Second
C : Third

COMPOSITION COMPONENT
0 : 168pin Buffered SIMM / DIMM
1 : 200pin Buffered DIMM
3 : 168pin Unbuffered DIMM
7 : 144pin Unbuffered SODIMM
8 : 80pin DIMM (Custom Module)

Old Part Numbering system before merger

DRAM MODULE PART NUMBERING (Cheong Ju)

64MD Based

GMM X 7 XX XX X X X X X XX - XX

HYNIX C-Site
Memory Module

MANUFACTURE
BLANK : LGS
S : Smart
T : Tanysis

FAMILY
7 : DRAM

ORGANIZATION
8 : x8
9 : x9
32 : x32
33 : x32 (2CAS)
34 : x32 (2WE)
36 : x36
64 : x64
65 : x64 (2CAS)
66 : x64 (2WE)
67 : x64 (4CAS)
72 : x72
73 : x72, ECC
14 : x144

DEPTH
1 : 1M
2 : 2M
4 : 4M
8 : 8M
16 : 16M
32 : 32M
64 : 64M

REFRESH
0 : 1K Refresh
1 : 2K Refresh
2 : 4K Refresh
3 : 8K Refresh

ACCESS/VOLTAGE MODE
5 : Fast Page Mode, 5V
6 : EDO Mode, 5V
7 : Fast Page Mode, 3.3V
8 : EDO Mode, 3.3V

SPEED
5 : 50ns
6 : 60ns
7 : 70ns

PACKAGE & TERMINAL
S : SOJ, Solder
SG : SOJ, Gold
T : TSOP, Solder
I : BLP, Solder
TG : TSOP, Gold

MDL REVISION NO.
BLANK : Original
N : First
M : Second
H : Height
(=1.5 Inch in 16M x 72 only)

IC REVISION NO.
BLANK : Original
A : First
B : Second
C : Third

COMPOSITION COMPONENT
0 : 168pin Buffered SIMM / DIMM
1 : 200pin Buffered DIMM
3 : 168pin Unbuffered DIMM
7 : 144pin Unbuffered SODIMM

Old Part Numbering system before merger

SDRAM MODULE PART NUMBERING (Cheong Ju)

GMM X 2 XX XX X X X X X XX - XXX

HYNIX C-Site
Memory Module

MANUFACTURE
NONE : LGS
S : Smart
T : Tanisys

FAMILY
2 : SDRAM

ORGANIZATION
64 : x64
72 : x72
73 : x72, ECC

DEPTH
1 : 1M (16M SD Based)
2 : 2M (16M SD Based)
4 : 4M (16M SD Based)
5 : 4M (64M SD Based)
6 : 4M (128M SD Based)
8 : 8M (16M SD Based)
9 : 8M (64M SD Based)
10 : 8M (128M SD Based)
16 : 16M (64M SD Based)
17 : 16M (128M SD Based)
32 : 32M (64M SD Based)
33 : 32M (128M SD Based)
64 : 64M (64M SD Based)
65 : 64M (128M SD Based)

REFRESH
0 : 1K Refresh
1 : 2K Refresh
2 : 4K Refresh
3 : 8K Refresh

INTERFACE
1 : LVTTL, 1Clock
2 : LVTTL, 2Clock
3 : LVTTL, 4Clock

SPEED
75 : 133MHz
8 : 125MHz
7K : PC100, 2-2-2^
7J : PC100, 3-2-2^^
10K : PC66*
10J : PC66**
12 : 83MHz
15 : 66MHz

PACKAGE & TERMINAL
T : TSOP, Solder
TG : TSOP, Gold
IG : BLP, Gold
SG : Stack, Gold

MODULE REVISION NO.
NONE : Original
N : First
F : 4Layer PCB
H : Height(=1.15" in 8M x 64 only)
P : with PLL

IC REVISION NO.
NONE : Original
A : First
B : Second
C : Third
D : Fourth
E : Fifth
F : Sixth

COMPOSITION COMPONENT
0 : 168pin Registered DIMM
1 : 200pin Registered DIMM
3 : 168pin Unregistered DIMM
7 : 144pin Unregistered SODIMM (Normal Power Based)
8 : 144pin Unregistered SODIMM (Low Power Based)

Note) ^ 7K means to meet tCK=10ns, CL=2, tAC=6ns, ^^ 7J means to meet tCK=10ns, CL=3, tAC=6ns
* 10K means to meet tCK=15ns, CL=2, tAC=9ns, ** 10J means to meet tCK=10ns, CL=3, tAC=9.5ns

Old Part Numbering system before merger

SLOW SRAM PART NUMBERING

HY XX X X XX XXX X XX XX - XX X

HYNIX MEMORY

PRODUCT GROUP

62 : Slow SRAM

POWER SUPPLY

BLANK : 5.0V
V : 3.3V
U : 3.0V
Q : 2.5V
S : 1.8V

PROCESS

BLANK : CMOS
F : Full CMOS

BIT ORGANIZATION

8 : x8 (* Blank : 256Kbit)
16 : x16

DENSITY

256 : 256Kbit
100 : 1M (Standard)
101 : 1M (1CS with /UB,/LB ; tCS)
200 : 2M (Standard)
201 : 2M (1CS with /UB,/LB ; tCS)
400 : 4M (Standard)
401 : 4M (2CS with /UB,/LB ; tCS)
402 : 4M (2CS with /UB,/LB ; tOE)
403 : 4M (1CS with /UB,/LB ; tCS)
404 : 4M (BHE with /UB,/LB ; tCS)
803 : 8M (1CS with /UB,/LB ; tCS)

VERSION

BLANK : 1st Generation
A : 2nd Generation
B : 3rd Generation
C : 4th Generation

TEMPERATURE

BLANK : 0°C ~ 70°C
E : - 25°C ~ 85°C
I : - 40°C ~ 85°C

SPEED

55 : 55ns
70 : 70ns
85 : 85ns
10 : 100ns
12 : 120ns

PACKAGE

P : PDIP
G : SOP
J : SOJ
M : uBGA
F : FBGA
T1 : TSOP- I
R1 : TSOP- I(Reversed)
ST : Small TSOP- I
SR : Small TSOP- I(Reversed)
T2 : TSOP- II
R2 : TSOP- II(Reversed)

POWER CONSUMPTION

BLANK : Standard
L : Low Power
LL : Low Low Power
SL : Super Low Power

Async. DRAM Component

TYPE	DENSITY	CONFIG. (word x bit)	PACKAGE	PART NUMBER	SUFFIX	FEATURES		REMARKS	SAMPLE AVAILABLE
						CYCLE (ns)	ACT./STD-BY (mA)		
FP/EDO COMPONENT	16Mb FP	4Mx4	24(26) SOJ. /24(26)TSOP-II	GM71C(S)16400C(L)/T	-5	50	90/1(0.15)	FP Mode,C- version	Now
					-6	60	80/1(0.15)	5V+/-10% Power Supply	
					-7	70	70/1(0.15)	4096 Refresh Cycles/64ms(Normal)	
								() ;4096Refresh Cycles/128ms(L- power)	
				GM71C(S)17400C(L)/T	-5	50	100/1(0.15)	FP Mode,C- version	Now
					-6	60	90/1(0.15)	5V+/-10% Power Supply	
					-7	70	80/1(0.15)	2048 Refresh Cycles/32ms(Normal)	
								2048 Refresh Cycles/128ms(L- power)	
				GM71V(S)16400C(L)/T	-5	50	90/1(0.1)	FP Mode,C- version	Now
					-6	60	80/1(0.1)	3.3V+/-0.3V Power Supply	
					-7	70	70/1(0.1)	4096 Refresh Cycles/64ms(Normal)	
								4096 Refresh Cycles/128ms(L- power)	
				GM71V(S)17400C(L)/T	-5	50	100/1(0.1)	FP Mode,C- version	Now
					-6	60	90/1(0.1)	3.3V+/-0.3V Power Supply	
					-7	70	80/1(0.1)	2048Refresh Cycles/32ms(Normal)	
								2048Refresh Cycles/128ms(L- power)	
				HY5116400CJ	-60	60	90/1	FP Mode, 3th generation	Now
								5V+/-10% Power Supply	
								4096 Refresh Cycles/32ms(Normal)	
				HY5117400CJ	-60	60	120/1	FP Mode, 3th generation	Now
								5V+/-10% Power Supply	
								2048 Refresh Cycles/32ms(Normal)	
				HY51V(S)16400HG(L)/T	-5	50	90/1(0.1)	FP Mode, G- version	Now
					-6	60	80/1(0.1)	3.3V+/-0.3V Power Supply	
					-7	70	70/1(0.1)	4096 Refresh Cycles/64ms(Normal)	
								4096 Refresh Cycles/128ms(L- power)	
				HY51V(S)17400HG(L)/T	-5	50	100/1(0.1)	FP Mode, G- version	Now
					-6	60	90/1(0.1)	3.3V+/-0.3V Power Supply	
					-7	70	80/1(0.1)	2048 Refresh Cycles/32ms(Normal)	
								2048 Refresh Cycles/128ms(L- power)	
		2Mx8	28pin SOJ /28pinTSOP-II	GM71C(S)17800C(L)/T	-5	50	110/1(0.15)	FP Mode, C- version	Now
					-6	60	100/1(0.15)	5V+/-10% Power Supply	
					-7	70	90/1(0.15)	2048 Refresh Cycles/32ms(Normal)	
								2048 Refresh Cycles/128ms(L- power)	
				GM71V(S)17800C(L)/T	-5	50	110/1(0.15)	FP Mode, C- version	Now
					-6	60	100/1(0.15)	3.3V+/-0.3V Power Supply	
					-7	70	90/1(0.15)	2048 Refresh Cycles/32ms(Normal)	
								2048 Refresh Cycles/128ms(L- power)	
		1Mx16	42SOJ /44(50)TSOP-II	GM71C(S)16160C(L)/T	-5	50	110/1(0.15)	FP Mode, C- version	Now
					-6	60	100/1(0.15)	5V+/-10% Power Supply	
					-7	70	90/1(0.15)	4096 Refresh Cycles/64ms(Normal)	
								4096 Refresh Cycles/128ms(L- power)	
				GM71C(S)18160C(L)/T	-5	50	190/1(0.15)	FP Mode, C- version	Now
					-6	60	170/1(0.15)	5V+/-10% Power Supply	
					-7	70	150/1(0.15)	1024 Refresh Cycles/16ms(Normal)	
								1024 Refresh Cycles/128ms(L- power)	
				GM71V(S)16160C(L)/T	-5	50	110/1(0.15)	FP Mode, C- version	Now
					-6	60	100/1(0.15)	3.3V+/-0.3V Power Supply	
					-7	70	90/1(0.15)	4096 Refresh Cycles/64ms(Normal)	
								4096 Refresh Cycles/128ms(L- power)	
				GM71V(S)18160C(L)/T	-5	50	190/1(0.15)	FP Mode, C- version	Now
					-6	60	170/1(0.15)	3.3V+/-0.3V Power Supply	
					-7	70	150/1(0.15)	1024 Refresh Cycles/16ms(Normal)	
								1024 Refresh Cycles/128ms(L- power)	

Async. DRAM Component

TYPE	DENSITY	CONFIG. (word x bit)	PACKAGE	PART NUMBER	SUFFIX	FEATURES		REMARKS	SAMPLE AVAILABLE
						CYCLE (ns)	ACT./STD-BY (mA)		
FP/EDO COMPONENT	16Mb FP	1Mx16	42SOJ /44(50)TSOP-II	GM71V18160CJ	-6E	60	170/1	FP Mode, C- version Extended Temp. part.(-30~85C) 3.3V+/-0.3V Power Supply 1024 Refresh Cycles/16ms(Normal)	Now
				HY51V(S)16160HG(L)J/T	-5 -6 -7	50 60 70	110/1(0.15) 100/1(0.15) 90/1(0.15)	FP Mode, G- version 3.3V+/-0.3V Power Supply 4096 Refresh Cycles/64ms(Normal) 4096 Refresh Cycles/128ms(L- power)	Now
				HY51V(S)18160HG(L)J/T	-5 -6 -7	50 60 70	190/1(0.15) 170/1(0.15) 150/1(0.15)	FP Mode, G- version 3.3V+/-0.3V Power Supply 1024 Refresh Cycles/16ms(Normal) 1042 Refresh Cycles/128ms(L- power)	Now
	16Mb EDO	4Mx4	24(26) SOJ /24(26)TSOP-II	GM71C(S)16403C(L)J/T	-5 -6 -7	50 60 70	90/1(0.15) 80/1(0.15) 70/1(0.15)	EDO Mode, C- version 5V+/-10% Power Supply 4096 Refresh Cycles/64ms(Normal) 4096 Refresh Cycles/128ms(L- power)	Now
				GM71C(S)17403C(L)J/T	-5 -6 -7	50 60 70	120/1(0.15) 110/1(0.15) 100/1(0.15)	EDO Mode, C- version 5V+/-10% Power Supply 2048 Refresh Cycles/32ms(Normal) 2048 Refresh Cycles/128ms(L- power)	Now
				GM71V(S)16403C(L)J/T	-5 -6 -7	50 60 70	90/1(0.15) 80/1(0.15) 70/1(0.15)	EDO Mode, C- version 3.3V+/-0.3V Power Supply 4096 Refresh Cycles/64ms(Normal) 4096 Refresh Cycles/128ms(L- power)	Now
				GM71V(S)17403C(L)J/T	-5 -6 -7	50 60 70	100/1(0.1) 90/1(0.1) 80/1(0.1)	EDO Mode, C- version 3.3V+/-0.3V Power Supply 2048 Refresh Cycles/32ms(Normal) 2048 Refresh Cycles/128ms(L- power)	Now
				GM71VLS17403CLT	-1	100	TBD	EDO Mode, C- version 2.35V Power Supply.	Now
				HY5116404CJ	-60	60	90/1	EDO Mode, 3th generation 5V+/-10% Power Supply 4096 Refresh Cycles/64ms(L- power)	Now
				HY5117404CJ	-60	60	120/1	EDO Mode, 3th generation 5V+/-10% Power Supply 2048 Refresh Cycles/32ms(L- power)	Now
				HY51V16404CJ	-60	60	80/0.5	EDO Mode, 3th generation 3.3V+/-0.3V Power Supply 4096 Refresh Cycles/64ms(L- power)	Now
				HY51V(S)16403HG(L)J/T	-5 -6 -7	50 60 70	90/1(0.1) 80/1(0.1) 70/1(0.1)	EDO Mode, G- version 3.3V+/-0.3V Power Supply 4096 Refresh Cycles/64ms(Normal) 4096 Refresh Cycles/128ms(L- power)	Now
				HY51V(S)17403HG(L)J/T	-5 -6 -7	50 60 70	100/1(0.1) 90/1(0.1) 80/1(0.1)	EDO Mode, G- version 3.3V+/-0.3V Power Supply 2048 Refresh Cycles/32ms(Normal) 2048 Refresh Cycles/128ms(L- power)	Now
				HY51VLS16(7/8)403HG(L)J/T	-10	100	TBD	EDO Mode, G- version 2.35V Operation	Now
		2Mx8	28pin SOJ /28pinTSOP-II	GM71C(S)17803C(L)J/T	-5 -6 -7	50 60 70	110/1(0.15) 100/1(0.15) 90/1(0.15)	EDO Mode, C- version 5V+/-10% Power Supply 2048 Refresh Cycles/32ms(Normal) 2048 Refresh Cycles/128ms(L- power)	Now

Note *: Extended temperature Part (-30˚C~ 85˚C)

Async. DRAM Component

TYPE	DENSITY	CONFIG. (word x bit)	PACKAGE	PART NUMBER	SUFFIX	FEATURES		REMARKS	SAMPLE AVAILABLE
						CYCLE (ns)	ACT./STD-BY (mA)		
FP/EDO COMPONENT	16Mb EDO	2Mx8	28pin SOJ /28pinTSOP-II	GM71V(S)17803C(L)/T	-5	50	110/1(0.15)	EDO Mode, C- version 3.3V+/-0.3V Power Supply 2048 Refresh Cycles/32ms(Normal) 2048 Refresh Cycles/128ms(L- power)	Now
				HY5117804BSLJ	-60	60	120/0.2	EDO Mode, 3th generation 5V+/-10% Power Supply 2048 Refresh Cycles/32ms Low power with self refresh	Now
		1Mx16	42SOJ /44(50)TSOP-II	GM71C(S)16163C(L)/T	-5	50	110/1(0.15)	EDO Mode, C- version 5V+/-10% Power Supply 4096 Refresh Cycles/64ms(Normal) 4096 Refresh Cycles/128ms(L- power)	Now
				GM71C(S)18163C(L)/T	-5	50	190/1(0.15)	EDO Mode, C- version 5V+/-10% Power Supply 1024Refresh Cycles/16ms(Normal) 1024Refresh Cycles/128ms(L- power)	Now
				GM71V18163CJ	-6E	60	170/1	EDO Mode, C- version Extended Temp. part.(-30~85C) 3.3V+/-0.3V Power Supply(ET Part) 1024 Refresh Cycles/16ms(Normal)	Now
				GM71V(S)16163C(L)/T	-5	50	110/1(0.15)	EDO Mode, C- version 3.3V+/-0.3V Power Supply 4096 Refresh Cycles/64ms(Normal) 4096 Refresh Cycles/128ms(L- power)	Now
				GM71V(S)18163C(L)/T	-5	50	190/1(0.15)	EDO Mode, C- version 3.3V+/-0.3V Power Supply 1024 Refresh Cycles/16ms(Normal) 1024 Refresh Cycles/128ms(L- power)	Now
				HY51V(S)16163HG(L)/T	-5	50	110/1(0.15)	EDO Mode, G- version 3.3V+/-0.3V Power Supply 4096 Refresh Cycles/64ms(Normal) 4096 Refresh Cycles/128ms(L- power)	Now
				HY51V(S)18163HG(L)/T	-5	50	190/1(0.15)	EDO Mode, G- version 3.3V+/-0.3V Power Supply 1024 Refresh Cycles/16ms(Normal) 1024 Refresh Cycles/128ms(L- power)	Now
	64Mb FP	16Mx4	32PinSOJ /TSOP-II	GM71V64400CJ/T	-5	50	120/0.5	FP Mode,C- version 3.3V+/-0.3V Power Supply 8192 Refresh Cycles/64ms(Normal)	Now
				GM71V65400CJ/T	-5	50	120/0.5	FP Mode, C- version 3.3V+/-0.3V Power Supply 4096 Refresh Cycles/64ms(Normal)	Now
				HY51V64400HGJ/T	-45	45	130/0.5	FP Mode, G- version 3.3V+/-0.3V Power Supply 8192 Refresh Cycles/64ms(Normal)	Now
				HY51V65400HGJ/T	-5	50	120/0.5 110/0.5	FP Mode, G- version 3.3V+/-0.3V Power Supply 4096 Refresh Cycles/64ms(Normal)	Now
		8Mx8	32PinSOJ /TSOP-II	GM71V65800CJ/T	-45	45	130/0.5	FP Mode, C- version 3.3V+/-0.3V Power Supply 4096 Refresh Cycles/64ms(Normal)	Now
					-5	50	120/0.5 110/0.5		
					-6	60	100/1(0.15)		
					-7	70	90/1(0.15)		
					-8	80	80/1(0.15)		

Note *: Extended temperature Part (-30˚C~ 85˚C)

Async. DRAM Component

TYPE	DENSITY	CONFIG. (word x bit)	PACKAGE	PART NUMBER	SUFFIX	FEATURES		REMARKS	SAMPLE AVAILABLE
						CYCLE (ns)	ACT./STD-BY (mA)		
F P / E D O C O M P O N E N T	64Mb EDO	16Mx4	32PinSOJ /TSOP-II	GM71V(S)64403C(L)J/T	-45	45	130/0.5(0.2)	EDO Mode, C- version 3.3V+/-0.3V Power Supply 8192 Refresh Cycles/64ms(Normal) 8192 Refresh Cycles/128ms(L- power)	Now
					-5	50	120/0.5(0.2)		
					-6	60	110/0.5(0.2)		
				GM71V(S)65403C(L)J/T	-5	50	140/0.5(0.3)	EDO Mode,C- version 3.3V+/-0.3V Power Supply 4096 Refresh Cycles/64ms(Normal) 4096 Refresh Cycles/128ms(L- power)	Now
					-6	60	130/0.5(0.3)		
				HY51V65404ATC	-50	50	140/0.5	EDO Mode, 3th generation 3.3V+/-0.3V Power Supply 4096 Refresh Cycles/64ms(Normal)	Now
				HY51V64403HG(L)J/T	-45	45	130/0.5	EDO Mode, G- version 3.3V+/-0.3V Power Supply 8192 Refresh Cycles/64ms(Normal)	Now
					-5	50	120/0.5		
					-6	60	120/0.5		
				HY51V65403HG(L)J/T	-45	45	130/0.5	EDO Mode, G- version 3.3V+/-0.3V Power Supply 4096 Refresh Cycles/64ms(Normal)	Now
					-5	50	120/0.5		
					-6	60	110/0.5		
		8Mx8	32PinSOJ /TSOP-II	GM71V(S)64803C(L)J/T	-5	50	125/0.5(0.3)	EDO Mode, C- version 3.3V+/-0.3V Power Supply 8192 Refresh Cycles/64ms(Normal) 8192 Refresh Cycles/128ms(L- power) CBR: 4096 Refresh Cycles , 64ms(Normal) /128ms(L- power)	Now
					-6	60	115/0.5(0.3)		
				GM71V(S)65803C(L)J/T	-5	50	145/0.5(0.3)	EDO Mode, C- version 3.3V+/-0.3V Power Supply 4096 Refresh Cycles/64ms(Normal) 4096 Refresh Cycles/128ms(L- power) CBR: same with RAS only refresh	Now
					-6	60	135/0.5(0.3)		
				HY51V64804ATC	-50	50	110/0.5	EDO Mode, 3th generation 3.3V+/-0.3V Power Supply 8192 Refresh Cycles/64ms(Normal) 8192 Refresh Cycles/128ms(L- power)	Now
					-60	60	90/0.5		
				HY51V65804ATC	-50	50	140/0.5	EDO Mode, 3th generation 3.3V+/-0.3V Power Supply 4096Refresh Cycles/64ms(Normal) 4096Refresh Cycles/128ms(L- power)	Now
					-60	60	120/0.5		
				HY51V(S)64803HG(L)J/T	-45	45	130/0.5(0.2)	EDO Mode, G- version 3.3V+/-0.3V Power Supply 8192 Refresh Cycles/64ms(Normal) 8192 Refresh Cycles/128ms(L- power)	Now
					-5	50	120/0.5(0.2)		
					-6	60	110/0.5(0.2)		
				HY51V(S)65803HG(L)J/T	-45	45	130/0.5(0.2)	EDO Mode, G- version 3.3V+/-0.3V Power Supply 4096 Refresh Cycles/64ms(Normal) 4096 Refresh Cycles/128ms(L- power)	Now
					-5	50	120/0.5(0.2)		
					-6	60	110/0.5(0.2)		
		4Mx16	50PinSOJ /TSOP-II	GM71V(S)65163C(L)J/T	-5	50	150/0.5(0.3)	EDO Mode, C- version 3.3V+/-0.3V Power Supply 4096 Refresh Cycles/64ms(Normal) 4096 Refresh Cycles/128ms(L- power) CBR: same with RAS only refresh	Now
					-6	60	140/0.5(0.3)		
				HY51V(S)65173HG(L)J/T	-45	45	130/0.5(0.2)	EDO Mode, G- version 3.3V+/-0.3V Power Supply 4096 Refresh Cycles/64ms(Normal) 4096 Refresh Cycles/128ms(L- power)	Now
					-5	50	120/0.5(0.2)		
					-6	60	110/0.5(0.2)		

SDRAM Component

TYPE	DENSITY	CONFIG. (word x bit)	PACKAGE	PART NUMBER	SUFFIX	FEATURES		REMARKS	SAMPLE AVAILABLE
						CYCLE (ns)	ACT./STD-BY (mA)		
SDR COMPONENT	16Mb	1Mx16 (512Kx16 x2bank)	400mil 50pin TSOP-II	HY57V161610DTC	-5	5	130/2	5th generation	Now
					-55	5.5	130/2	VDD = 3.3V+/-0.3V	
					-6	6	120/2	4096 Refresh cycles / 64ms	
					-7(I)	7	110/2	LVTTL Interface.	
					-8	8	110/2	(I) ; Industrial Temp. part.(-40~85C)	
					-10	10	110/2		
				GM72V161621E(L)T	-7	7	120/1(0.4)	E version	Now
					-75	7.5	110/1(0.4)	VDD = 3.3V+/-0.3V	
					-8	8	100/1(0.4)	4096 Refresh cycles / 64ms	
								Auto and Self refresh capability	
								Programmable CAS Latency	
								LVTTL Interface.	
	64Mb	16Mx4 (4Mx4 x4bank)	54pin TSOP-II	GM72V66441ET	-7	7	85/1	E version	Now
					-75	7.5	85/1	VDD = 3.3V +/- 0.3V	
					-8	8	80/1	4096 Refresh cycles / 64ms	
					-7K	10	80/1	LVTTL Interface.	
					-7J	10	80/1		
				HY57V654020BTC	-6	6	110/2	4th Generation	Now
					-75	7.5	90/2	VDD = 3.3V +/- 0.3V	
					-8	8	80/2	4096 Refresh cycles / 64ms	
					-10P	10	70/2	LVTTL Interface.	
					-10S	10	70/2		
					-10	10	60/2		
				HY57V64420HGT	-6	6	TBD	G version	Now
					-7	7	85/1	VDD = 3.3V +/- 0.3V	
					-K	7.5	85/1	4096 Refresh cycles / 64ms	
					- H	7.5	85/1	LVTTL Interface.	
					- P	10	80/1		
					- S	10	80/1		
		8Mx8 (2Mx8 x4bank)	400mil 54pin TSOP-II	GM72V66841ET	-7	7	85/1	E version	Now
					-75	7.5	85/1	VDD = 3.3V +/- 0.3V	
					-8	8	80/1	4096 Refresh cycles / 64ms	
					-7K	7	80/1	LVTTL Interface.	
					-7J	7	80/1		
				HY57V658020BTC	-75(I)	7.5	90/2	4th Generation	Now
					-8	8	80/2	VDD = 3.3V +/- 0.3V	
					-10P	10	70/2	4096 Refresh cycles / 64ms	
					-10S	10	70/2	LVTTL Interface.	
					-10	10	60/2	(I) ; Industrial Temp. Part (-40 ~ 85C)	
				HY57V64820HGT	-6	6	TBD	G version	Now
					-7	7	85/1	VDD = 3.3V +/- 0.3V	
					-K	7.5	85/1	4096 Refresh cycles / 64ms	
					-H	7.5	85/1	LVTTL Interface.	
					-P	10	80/1		
					-S	10	80/1		
		4Mx16 (1Mx16 x4bank)	400mil 54pin TSOP-II	HY57V651620B(L)TC	-6	6	110/2	4th Generation	Now
					-7	7	100/2	VDD = 3.3V +/- 0.3V	
					-75(I)	7.5	90/2(0.5)	4096 Refresh cycles / 64ms	
					-8	8	80/2	LVTTL Interface.	
					-10P	10	70/2	(I) ; Industrial Temp. Part (-40 ~ 85C)	
					-10S(I)	10	70/2(0.5)		
					-10	10	60/2		
				HY57V641620HG(L)T	-6	6	TBD	G version	Now
					-7	7	85/1	VDD = 3.3V +/- 0.3V	
					-K	7.5	85/1	4096 Refresh cycles / 64ms	
					-H	7.5	85/1(0.4)	LVTTL Interface.	
					-P	10	80/1		
					-S	10	80/1(0.4)		

SDRAM Component

TYPE	DENSITY	CONFIG. (word x bit)	PACKAGE	PART NUMBER	SUFFIX	FEATURES CYCLE (ns)	FEATURES ACT./STD-BY (mA)	REMARKS	SAMPLE AVAILABLE
SDR COMPONENT	64Mb	2Mx32 (512Kx32 x4bank)	400mil 86pin TSOP-II	HY57V653220BTC	-55	5.5	190/2	4th Generation	Now
					-6	6	180/2	VDD = 3.3V +/- 0.3V	
					-7(I)	-7	170/2	4096 Refresh cycles / 64ms	
					-8	-8	150/2	LVTTL Interface.	
					-10(I)	-10	150/2	Industrial Temp. Part (-40 ~ 85C)	
				HY57V643220CT	-5	5	200/2	5th Generation	Now
					-55	5.5	190/2	VDD = 3.3V +/- 0.3V	
					-6	6	180/2	4096 Refresh cycles / 64ms	
					-7	7	170/2	LVTTL Interface.	
					-8	8	150/2		
	128Mb	32Mx4 (8Mx8 x4bank)	400mil 54pin TSOP-II	HY57V1294020TC	-75	7.5	130/2	2nd Generation	Now
					-8	8	120/2	VDD = 3.3V +/- 0.3V	
					-10P	10	120/2	4096 Refresh cycles / 64msec	
					-10S	10	120/2	LVTTL Interface.	
					-10	10	105/2		
				HY57V28420AT	-6	6	120/2	3rd Generation	Now
					-K	7.5	110/2	VDD = 3.3V +/- 0.3V	
					-H	7.5	110/2	4096 Refresh cycles / 64msec	
					-8	8	100 / 2	LVTTL Interface.	
					-P	10	100 / 2		
					-S	10	100 / 2		
					-10	10	90 / 2		
				HY57V28420HCT	-55	5.5	TBD	C Version	Now
					-6	6	120 / 2	VDD = 3.3V +/- 0.3V	
					-K	7.5	110 / 2	4096 Refresh cycles / 64msec	
					-H	7.5	110 / 2	LVTTL Interface.	
					-8	8	110 / 2		
					-P	10	100 / 2		
					-S	10	100 / 2		
				GM72V28441AT	-8	8	110 / 2	A Version	Now
					-7K	10	110 / 2	VDD = 3.3V +/- 0.3V	
					-7J	10	110 / 2	4096 Refresh cycles / 64msec	
								LVTTL Interface.	
		16Mx8 (4Mx8 x4bank)	400mil 54pin TSOP-II	HY57V1298020TC	-75	7.5	130 / 2	2nd Generation	Now
					-8	8	120 / 2	VDD = 3.3V +/- 0.3V	
					-10P	10	120 / 2	4096 Refresh cycles / 64msec	
					-10S	10	120 / 2	LVTTL Interface.	
					-10	10	105 / 2		
				HY57V28820AT	-6	6	120 / 2	3rd Generation	Now
					-K(I)	7.5	110 / 2	VDD = 3.3V +/- 0.3V	
					-H(I)	7.5	110 / 2	4096 Refresh cycles / 64msec	
					-8	8	100 / 2	LVTTL Interface.	
					-P(I)	10	100 / 2	(I) . Industrial Temp.part (-40 ~ 80C)	
					-S(I)	10	100 / 2		
					-10	10	90 / 2		
				HY57V28820HCT	-55	5.5	TBD	C Version	Now
					-6	6	120/ 2	VDD = 3.3V +/- 0.3V	
					-K	7.5	110 / 2	4096 Refresh cycles / 64msec	
					-H	7.5	110 / 2	LVTTL Interface.	
					-8	8	110 / 2		
					-P	10	100 / 2		
					-S	10	100 / 2		
				GM72V28841AT	-8	8	120 / 2	A Version	Now
					-7K	10	120 / 2	VDD = 3.3V +/- 0.3V	
					-7J	10	120 / 2	4096 Refresh cycles / 64msec	
								LVTTL Interface.	
		8Mx16 (2Mx16 x4bank)	400mil 54pin TSOP-II	HY57V1291620(L)TC	-75	7.5	130 / 2(0.8)	2nd Generation	Now
					-8	8	120 / 2	VDD = 3.3V +/- 0.3V	
					-10P	10	120 / 2	4096 Refresh cycles / 64msec	
					-10S	10	120 / 2(0.8)	LVTTL Interface.	
					-10	10	105 / 2		

Note *: Extended temperature Part (-40˚C~ 85˚C)

SDRAM Component

TYPE	DENSITY	CONFIG. (word x bit)	PACKAGE	PART NUMBER	SUFFIX	FEATURES CYCLE (ns)	FEATURES ACT./STD-BY (mA)	REMARKS	SAMPLE AVAILABLE
SDR COMPONENT	128Mb	8Mx16 (2Mx16 x4bank)	400mil 54pin TSOP-II	HY57V281620A(L)T	-6 -K(I) -H(I) -8 -P(I) -S(I) -10	6 7.5 7.5 8 10 10 10	120 / 2 110 / 2 110 / 2(0.8) 100 / 2 100 / 2(0.8) 100 / 2(0.8) 90 / 2	3rd Generation VDD = 3.3V +/- 0.3V 4096 Refresh cycles / 64msec LVTTL Interface. (I) ; Industrial Temp.part (-40 – 80C)	Now
				HY57V281620HC(L)T	-55 -6 -K -H -8 -P -S	5.5 6 7.5 7.5 8 10 10	TBD 130 / 2 120 / 2 120 / 2(0.8) 120 / 2 110 / 2(0.8) 110 / 2(0.8)	C Version VDD = 3.3V +/- 0.3V 4096 Refresh cycles / 64msec LVTTL Interface.	Now
				GM72V281641AT	-8 -7K -7J	8 10 10	130 / 2 130 / 2 130 / 2	A Version VDD = 3.3V +/- 0.3V 4096 Refresh cycles / 64msec LVTTL Interface.	Now
				HY57W281620HCT	-H -P -S	7.5 10 10	110/TBD 100/TBD 100/TBD	C Version VDD = 2.5V +/- 0.2V PASR (Partial Array Self Refresh) DPDM (Deep Power Down Mode) TCSR (Temperature Compensated Self Ref.) LVTTL compatible I/O Interface	4Q
			54 Ball FBGA	HY5W26CF	-H -P -S	7.5 10 10	110/TBD 100/TBD 100/TBD	C Version VDD = 2.5V +/- 0.2V PASR (Partial Array Self Refresh) DPDM (Deep Power Down Mode) TCSR (Temperature Compensated Self Ref.) LVTTL compatible I/O Interface	4Q
	256Mb	64Mx4 (16Mx4 x4bank)	400mil 54Pin TSOP-II	HY57V56420T	-H -S	7.5 10	120 / 4 100 / 4	1st Generation VDD = 3.3V +/- 0.3V 8192 Refresh cycles/ 64ms LVTTL Interface.	Now
				HY57V56420AT	-H -P -S	7.5 10 10	120 / 2 110 / 2 110 / 2	2nd Generation VDD = 3.3V +/- 0.3V 8192 Refresh cycles/ 64ms LVTTL Interface.	3Q
				HY57V56420HDT	-H -P -S	7.5 10 10	TBD TBD TBD	D Version VDD = 3.3V +/- 0.3V 8192 Refresh cycles/ 64ms LVTTL Interface.	3Q
		32Mx8 (8Mx8 x4bank)	400mil 54Pin TSOP-II	HY57V56820T	-H -S	7.5 10	120 / 4 100 / 4	1st Generation VDD = 3.3V +/- 0.3V 8192 Refresh cycles/ 64ms LVTTL Interface.	Now
				HY57V56820AT	-H -P -S	7.5 10 10	120 / 2 110 / 2 110 / 2	2nd Generation VDD = 3.3V +/- 0.3V 8192 Refresh cycles/ 64ms LVTTL Interface.	3Q
				HY57V56820HDT	-H -P -S	7.5 10 10	TBD TBD TBD	D Version VDD = 3.3V +/- 0.3V 8192 Refresh cycles/ 64ms LVTTL Interface.	3Q
		16Mx16 (4Mx16 x4bank)	400mil 54Pin TSOP-II	HY57V561620(L)T	-H(I) -S(I)	7.5 10	120 / 4 100 / 4	1st Generation VDD = 3.3V +/- 0.3V 8192 Refresh cycles/ 64ms LVTTL Interface. Industrial Temp. part (-40~85C)	Now
				HY57V561620A(L)T	-H -P -S	7.5 10 10	120 / 2(1) 110 / 2 110 / 2(1)	2nd Generation VDD = 3.3V +/- 0.3V 8192 Refresh cycles/ 64ms LVTTL Interface.	3Q
				HY57V561620HD(L)T	-H -P -S	7.5 10 10	TBD TBD TBD	D Version VDD = 3.3V +/- 0.3V 8192 Refresh cycles/ 64ms LVTTL Interface.	3Q

Note **: Industrial temperature Part (-40˚C ~ 85˚C).

DDR SDRAM Component

TYPE	DENSITY	CONFIG. (word x bit)	PACKAGE	PART NUMBER	SUFFIX	FEATURES		REMARKS	SAMPLE AVAILABLE
						CYCLE (ns)	ACT./STD-BY (mA)		
DDR COMPONENT	64Mb	2Mx32 (512Kx32 x4bank)	100pin LQFP	HY5DU663222Q	-55	5.5	270 / 4	4th Generation	Now
					-6	6	260 / 4	VDD/VDDQ = 2.8V +/- 0.28	
					-(7)	7	240 / 4	2048 Refresh cycles / 16msec	
								(): 2.5V available	
								SSTL-2 Interface	
				HY5DU643222AQ	-4	4	TBD	6th Generation	3Q
					-43	4.3		VDD/VDDQ = 2.5V +/- 0.125	
					-5	5		4096 Refresh cycles / 32msec	
					-55	5.5		SSTL-2 Interface	
					-6	6			
					-7	7			
			144Ball FBGA	HY5DU643222AF	-4	4	TBD	6th Generation	4Q
					-43	4.3		VDD/VDDQ = 2.5V +/- 5%	
					-5	5		4096 Refresh cycles / 32msec	
								SSTL-2 Interface	
		4Mx16 (1Mx16 x4bank)	400mil 66pin TSOP-II	HY5DV651622TC	-G55	5.5	160 / 2	4th Generation	Now
					-G6	6	150 / 2	VDD= 3.3V + 0.3 V /- 0.15 V	
					-G7	7	140 / 2	VDDQ= 2.5V +/- 0.2 V	
								4096 Refresh cycles / 64msec	
								SSTL-2 Interface	
				HY5DU641622AT	-5	5	TBD	5th Generation	Now
					-55	5.5		VDD/VDDQ = 2.5V +/- 0.125	
								4096 Refresh cycles / 64msec	
								SSTL-2 Interface	
				HY5DV641622AT	-33	3.3	TBD	5th Generation	Now
					-36	3.6		VDD/VDDQ = 3.3V +/- 0.3 V	
					-4	4		4096 Refresh cycles / 64msec	
					-43	4.3		SSTL-2 Interface	
					-5	5			
	128Mb	32Mx4 (8Mx4 x4bank)	400mil 66pin TSOP-II	HY5DU28422T	- H	7.5	130 / 2	2nd Generation	Now
					- L	10	120 / 2	VDD/VDDQ = 2.5 V +/- 0.2 V	
								4096 Refresh cycles / 64msec	
								SSTL-2 Interface	
				HY5DU28422AT	- K	7.5	140 / 2	3rd Generation	Now
					- H	7.5	130 / 2	VDD/VDDQ = 2.5 V +/- 0.2 V	
					- L	10	120 / 2	4096 Refresh cycles / 64msec	
								SSTL-2 Interface	
		16Mx8 (4Mx8 x4bank)	400mil 66pin TSOP-II	HY5DU28822T	- H	7.5	140 / 2	2nd Generation	Now
					- L	10	130 / 2	VDD/VDDQ = 2.5 V +/- 0.2 V	
								4096 Refresh cycles / 64msec	
								SSTL-2 Interface	
				HY5DU28822AT	- K	7.5	140 / 2	3rd Generation	Now
					- H	7.5	130 / 2	VDD/VDDQ = 2.5 V +/- 0.2 V	
					- L	10	120 / 2	4096 Refresh cycles / 64msec	
								SSTL-2 Interface	
		8Mx16 (2Mx16 x4bank)	400mil 66pin TSOP-II	HY5DU281622T	- H	7.5	150 / 2	2nd Generation	Now
					- L	10	140 / 2	VDD/VDDQ = 2.5 V +/- 0.2 V	
								4096 Refresh cycles / 64msec	
								SSTL-2 Interface	
				HY5DU281622AT	- K	7.5	160 / 2	3rd Generation	Now
					- H	7.5	150 / 2	VDD/VDDQ = 2.5 V +/- 0.2 V	
					- L	10	140 / 2	4096 Refresh cycles / 64msec	
								SSTL-2 Interface	

DDR SDRAM Component

TYPE	DENSITY	CONFIG. (word x bit)	PACKAGE	PART NUMBER	SUFFIX	FEATURES		REMARKS	SAMPLE AVAILABLE
						CYCLE (ns)	ACT./STD-BY (mA)		
DDR COMPONENT	128Mb	4Mx32 (1Mx32 x4bank)	100pin LQFP	HY5DU283222Q	-4	4	TBD	4th Generation VDD/VDDQ = 2.5V +/- 0.2 V 4096 Refresh cycles / 32msec SSTL-2 Interface	3Q
					-43	4.3			
					-5	5			
			LF-CSP 144 Ball	HY5DU283222F	-4	4	TBD	4th Generation VDD/VDDQ = 2.5V +/- 0.2 V 4096 Refresh cycles / 64msec SSTL-2 Interface	4Q
					-45	4.5			
					-5	5			
				HY5DV283222F	-33	3.3	TBD	4th Generation VDD/VDDQ = 3.3V +/- 0.3 V 4096 Refresh cycles / 64msec SSTL-2 Interface	4Q
					-4	4			
	256Mb	64Mx4 (16Mx4 x4bank)	400mil 66pin TSOP-II	HY5DU56422T	- K	7.5	120 / 3	2nd Generation VDD/VDDQ = 2.5 V +/- 0.2 V 8192 Refresh cycles / 64msec SSTL-2 Interface	4Q
					- H	7.5	120 / 3		
					- L	10	110 / 3		
		32Mx8 (8Mx8 x4bank)	400mil 66pin TSOP-II	HY5DU56822T	- K	7.5	120 / 3	2nd Generation VDD/VDDQ = 2.5 V +/- 0.2 V 8192 Refresh cycles / 64msec SSTL-2 Interface	4Q
					- H	7.5	120 / 3		
					- L	10	110 / 3		
		16Mx16 (4Mx16 x4bank)	400mil 66pin TSOP-II	HY5DU561622T	- K	7.5	120 / 3	2nd Generation VDD/VDDQ = 2.5 V +/- 0.2 V 8192 Refresh cycles / 64msec SSTL-2 Interface	4Q
					- H	7.5	120 / 3		
					- L	10	110 / 3		

Direct RDRAM Component

TYPE	DENSITY	CONFIG. (word x bit)	PACKAGE	PART NUMBER	SUFFIX	FEATURES		REMARKS	SAMPLE AVAILABLE
						CYCLE (ns)	ACT./STD-BY (mA)		
DRD COMPONENT	128Mb	8Mx16 (256Kx16 x32bank)	62Ball uBGA	HY5R128HC	-653	600MHz	760 / 4.5	A-version 2.5V+/- 5% power supply Center bonding tRAC= 53ns,45ns,40ns	Now
					-745	711MHz			
	144Mb	8Mx18 (256Kx18 x32bank)	62Ball uBGA	HY5R144HC	-653	600MHz	670 / 4.5	A-version 2.5V+/- 5% power supply Center bonding tRAC= 53ns,45ns,40ns	Now
					-745	711MHz			
	256Mb	16Mx16 (512Kx16 x32bank)	92Ball uBGA	HY5R256HC	-653	600MHz	650 / 4.2	A-version 2.5V+/- 5% power supply Center bonding tRAC= 53ns,45ns,40ns	3Q
					-745	711MHz			
					-845	800MHz			
					-840	800MHz			
	288Mb	16Mx18 (512Kx18 x32bank)	92Ball uBGA	HY5R288HC	-653	600MHz	650 / 4.2	A-version 2.5V+/- 5% power supply Center bonding tRAC= 53ns,45ns,40ns	Now
					-745	711MHz			
					-845	800MHz			
					-840	800MHz			

Async. DRAM Module

TYPE		CONFIG. (Capacity)	PART NUMBER	SUFFIX	FEATURES		REMARKS	SAMPLE AVAILABLE
					CYCLE (ns)	ACT./STD-BY (mA)		
FP/EDO MODULE	72Pin SIMM	4Mx32 (16MB)	GMM7324100CNS/SG	-6	60	880/8	16Mb-C ver based 5V+/-0.5V Power Supply GM71C17400CJx8pcs(1bank) 2048Refresh Cycles/32ms	Now
				-7	70	800/8		
				-8	80	720/8		
			GMM7324110CNS/SG	-6	60	880/8	16Mb-C ver based 5V+/-0.5V Power Supply GM71C17403CJx8pcs(1bank) 2048Refresh Cycles/32ms	Now
				-7	70	800/8		
				-8	80	720/8		
		8Mx32 (32MB)	GMM7328100CS/SG	-6	60	896/16	16Mb-C ver component based 5V+/-0.5V Power Supply GM71C17400Cx16pcs(2bank) 2048Refresh Cycles/32ms	Now
				-7	70	816/16		
				-8	80	736/16		
			GMM7328110CS/SG	-6	60	896/16	16Mb-C ver component based 5V+/-0.5V Power Supply GM71C17403Cx16pcs(2bank) 2048Refresh Cycles/32ms	Now
				-7	70	816/16		
				-8	80	736/16		
	168 Pin DIMM	8Mx72 (64MB)	GMM7738280CTG	-5	50	1325/24.5	64Mb-C ver component based 3.3V+/-0.3V Power Supply GM71V65800Cx9pcs(1bank) 4096Refresh Cycles/64ms	Now
				-6	60	1235/24.5		
			HYMA6V8730E18HGTG	-5	50	1325/24.5	64Mb-G ver component based 3.3V+/-0.3V Power Supply HY51V65803HGx9pcs(1bank) 4096Refresh Cycles/64ms	Now
				-6	60	1235/24.5		
		16Mx72 (128MB)	GMM7316370CHTG	-5	50	TBD	64Mb-C ver component based 3.3V+/-0.3V Power Supply GM71V64400Cx18pcs(1bank) 8192Refresh Cycles/64ms	Now
			GMM7316380CTG	-5	50	2540/29	64Mb-C ver component based 3.3V+/-0.3V Power Supply GM71V64403Cx18pcs(1bank) 8192Refresh Cycles/64ms	Now
				-6	60	2396/29		
			HYMA6V16733F14HGTG	-45	45	2160/29	64Mb-G ver component based 3.3V+/-0.3V Power Supply HY51V64800HGx18pcs(2bank) 8192Refresh Cycles/64ms	Now
				-5	50	1820/29		
			HYMA6V16730E14HGTG	-45	45	2540/29	64Mb-G ver component based 3.3V+/-0.3V Power Supply HY51V65803HGx18pcs(2bank) 4096Refresh Cycles/64ms	Now
				-5	50	2360/29		
			HYMA6V16733E14HGTG	-45	45	2540/29	64Mb-G ver component based 3.3V+/-0.3V Power Supply HY51V64803HGx18pcs(2bank) 8192Refresh Cycles/64ms	Now
				-5	50	2360/29		
		32Mx72 (256MB)	GMM7332380CNTG	-5	50	2586/48	64Mb-C ver component based 3.3V+/-0.5V Power Supply GM71V64403Cx36pcs(2bank) 8192Refresh Cycles/64ms	Now
				-6	60	2406/48		
			HYMA6V32730E14HGTG	-45	45	2586/48	64Mb-G ver component based 3.3V+/-0.3V Power Supply HY51V65403HGx36pcs(2bank) 4096Refresh Cycles/64ms	Now
				-5	50	2406/48		
			HYMA6V32733E14HGTG	-45	45	2226/48	64Mb-G ver based 3.3V+/-0.3V Power Supply HY51V64403HGx36pcs(2bank) 8192Refresh Cycles/64ms	Now
				-5	50	2046/48		
	144Pin SODIMM	8Mx64 (64MB)	GMM765820787CNTG	-5	50	608 / 4	64Mb-C ver based 3.3V+/-0.3V Power Supply GM71V65163Cx8pcs(2bank) 4096esh Cycles/64ms	Now
				-6	60	568 / 4		

SDRAM Module

TYPE		CONFIG. (Capacity)	PART NUMBER	SUFFIX	FEATURES		REMARKS	SAMPLE AVAILABLE
					CYCLE (ns)	ACT./STD-BY (mA)		
SDR MODULE	168pin Unbuffered DIMM (Non ECC)	4Mx64 (32MB)	HYM7V63401BTRG	- 75	7.5	360 / 8	64Mb 4th generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V651620BTC x 4pcs(1Bank)	Now
			HYM76V4655HGT6	- P - S	10 10	280 / 8 280 / 8	64Mb G version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V641620HGT x 4pcs(1Bank)	Now
			HYM76V4635HGT6	- K - H	7.5 7.5	360 / 8 360 / 8	64Mb G version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V641620HGT x 4pcs(1Bank)	Now
		8Mx64 (64MB)	HYM7V65801BTFG	- 10P - 10S	10 10	560 / 16 560 / 16	64Mb 4th generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V658020BTC x 8pcs(1Bank)	Now
			HYM7V63801BTFG	- 75	7.5	720 / 16	64Mb 4th generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V658020BTC x 8pcs(1Bank)	Now
			GMM2649233ETG	- 75 - 7K - 7J	7.5 10 10	650 / 8 600 / 8 600 / 8	64Mb E version based VDD = 3.3V +/- 0.3V (LVTTL) GM72V66841ET x 8pcs(1Bank)	Now
			GMM2649233EFTG	- 75 - 7K - 7J	7.5 10 10	650 / 8 600 / 8 600 / 8	64Mb E version based VDD = 3.3V +/- 0.3V (LVTTL) GM72V66841ET x 8pcs(1Bank)	Now
			HYM76V8655HGT8	- P - S	10 10	560 / 16 560 / 16	64Mb G version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V64820HGT x 8pcs(1Bank)	Now
			HYM76V8635HGT8	- K - H	7.5 7.5	720 / 16 720 / 16	64Mb G version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V64820HGT x 8pcs(1Bank)	Now
			HYM71V8655AT6	-P -S	10 10	400 / 8 400 / 8	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V281620AT x4pcs(1bank)	Now
			HYM71V8635AT6	- K - H	7.5 7.5	440 / 8 400 / 8	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V281620AT x4pcs(1bank)	Now
			HYM71V8655HCT6	-P -S	10 10	440 / 3.2 440 / 3.2	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V281620HCT x4pcs(1bank)	Now
			HYM71V8635HCT6	-K -H	7.5 7.5	480 / 3.2 480 / 3.2	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V281620HCTx4pcs(1bank)	Now
		16Mx64 (128MB)	HYM7V651601BTFG	- 10P - 10S	10 10	800 / 32 800 / 32	64Mb 4th generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V658020BTC x 16pcs(2Bank)	Now
			HYM7V631601BTFG	- 75	7.5	960 / 32	64Mb 4th generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V658020BTC x 16pcs(2Bank)	Now
			GMM26416223ENTG	- 7K - 7J	10 10	700 / 16 700 / 16	64Mb E version based VDD = 3.3V +/- 0.3V (LVTTL) GM72V66841ET x 16pcs(2Bank)	Now
			HYM76V16655HGT8	- P - S	10 10	800 / 32 800 / 32	64Mb G version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V64820HGT x 16pcs(2Bank)	Now
			HYM76V16635HGT8	- K - H	7.5 7.5	960 / 32 960 / 32	64Mb G version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V64820HGT x 16pcs(2Bank)	Now
			HYM71V16655AT8	-P -S	10 10	800 / 16 800 / 16	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820ATx8pcs(1bank)	Now
			HYM71V16635AT8	-K -H	7.5 7.5	880 / 16 880 / 16	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820ATx8pcs(1bank)	Now

SDRAM Module

TYPE		CONFIG. (Capacity)	PART NUMBER	SUFFIX	FEATURES		REMARKS	SAMPLE AVAILABLE
					CYCLE (ns)	ACT./STD-BY (mA)		
SDR MODULE	168pin Unbuffered DIMM (Non ECC)	16Mx64 (128MB)	HYM71V16655AT8M	-P -S	10 10	800 / 16 800 / 16	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820ATx8pcs(1bank) PCB height : 1.25 inch,4 Layer PCB	Now
			HYM71V16635AT8M	-K -H	7.5 7.5	960 / 16 880 / 16	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V281620ATx8pcs(1bank) PCB height : 1.25 inch,4 Layer PCB	Now
			HYM71V16655HCT8	-P -S	10 10	800 / 6.4 800 / 6.4	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820HCTx8pcs(1bank)	Now
			HYM71V16635HCT8	-K -H	7.5 7.5	880 / 6.4 880 / 6.4	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820HCTx8pcs(1bank)	Now
			HYM71V16655HCT8M	-P -S	10 10	800 / 6.4 800 / 6.4	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820HCTx8pcs(1bank) PCB height : 1.25 inch,4 Layer PCB	Now
			HYM71V16635HCT8M	-K -H	7.5 7.5	880 / 6.4 880 / 6.4	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820HCTx8pcs(1bank) PCB height : 1.25 inch,4 Layer PCB	Now
		32Mx64 (256MB)	HYM71V32635AT8	-K -H	7.5 7.5	1200 / 32 1200 / 32	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820ATx16pcs(2banks)	Now
			HYM71V32655AT8	-P -S	10 10	1120 / 32 1120 / 32	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820ATx16pcs(2banks)	Now
			HYM71V32655HCT8	-P -S	10 10	1120 / 32 1120 / 32	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820HCTx16pcs(2banks)	Now
			HYM71V32635HCT8	-K -H	7.5 7.5	1200 / 12.8 1200 / 12.8	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820HCTx16pcs(2banks)	Now
			HYM71V32655HCT8M	-P -S	10 10	1120 / 32 1120 / 32	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820HCTx16pcs(2banks) PCB height : 1.25 inch,4 Layer PCB	Now
			HYM71V32635HCT8M	-K -H	7.5 7.5	1200 / 12.8 1200 / 12.8	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820HCTx16pcs(2banks) PCB height : 1.25 inch,4 Layer PCB	Now
			HYM72V32656T8 HYM72V32636T8	- S - H	10 7.5	800 / 32 880 / 32	256Mb 1st Generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V56820T x 8pcs (1Bank)	Now
			HYM72V32636AT8 HYM72V32656AT8 HYM72V32656AT8	- H - P - S	7.5 10 10	TBD	256Mb 2nd Generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V56820AT x 8pcs (1Bank)	3Q
			HYM72V32636HDT8 HYM72V32656HDT8 HYM72V32656HDT8	- H - P - S	7.5 10 10	TBD	256Mb D Version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V56820HDT x 8pcs (1Bank)	3Q
		64Mx64 (512MB)	HYM72V64656T8 HYM72V64636T8	- S - H	10 7.5	1040 / 64 1200 / 64	256Mb 1st Generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V56820T x 16pcs (2Bank)	Now
			HYM72V64636AT8 HYM72V64656AT8 HYM72V64656AT8	- H - P - S	7.5 10 10	TBD	256Mb 2nd Generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V56820AT x 16pcs (2Bank)	3Q
			HYM72V64636HDT8 HYM72V64656HDT8 HYM72V64656HDT8	- H - P - S	7.5 10 10	TBD	256Mb D Version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V56820HDT x 16pcs (2Bank)	3Q

SDRAM Module

TYPE		CONFIG. (Capacity)	PART NUMBER	SUFFIX	FEATURES		REMARKS	SAMPLE AVAILABLE
					CYCLE (ns)	ACT./STD-BY (mA)		
SDR MODULE	168pin Unbuffered DIMM (ECC)	8Mx72 (64MB)	HYM7V75A801BTFG	- 10P - 10S	10 10	630 / 18 630 / 18	64Mb 4th generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V658020BTC x 9pcs(1Bank)	Now
			HYM7V73A801BTFG	- 75	7.5	810 / 18	64Mb 4th generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V658020BTC x 9pcs(1Bank)	Now
			GMM2739223ETG	- 7K - 7J	10 10	650 / 9 650 / 9	64Mb E version based VDD = 3.3V +/- 0.3V (LVTTL) GM72V66841ET x 9pcs(1Bank)	Now
			HYM76V8755HGT8	- P - S	10 10	630 / 18 630 / 18	64Mb G version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V64820HGT x 9pcs(1Bank)	Now
			HYM76V8735HGT8	- K - H	7.5 7.5	810 / 18 810 / 18	64Mb G version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V64820HGT x 9pcs(1Bank)	Now
		16Mx72 (128MB)	HYM7V75A1601BTFG	- 10P - 10S	10 10	900 / 36 900 / 36	64Mb 4th generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V658020BTC x 18pcs(2Bank)	Now
			HYM7V73A1601BTFG	- 75	7.5	1080 / 36	64Mb 4th generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V658020BTC x 18pcs(2Bank)	Now
			GMM2731623ENTG	- 7K - 7J	10 10	850 / 18 850 / 18	64Mb E version based VDD = 3.3V +/- 0.3V (LVTTL) GM72V66841ET x 18pcs(2Bank)	Now
			HYM76V16755HGT8	- P - S	10 10	900 / 36 900 / 36	64Mb G version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V64820HGT x 18pcs(2Bank)	Now
			HYM76V16735HGT8	- K - H	7.5 7.5	1080 / 36 1080 / 36	64Mb G version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V64820HGT x 18pcs(2Bank)	Now
			HYM71V16755AT8	-P -S	10 10	900 / 18 900 / 18	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820ATx9pcs(1bank)	Now
			HYM71V16735AT8	-K -H	7.5 7.5	990 / 18 900 / 18	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820ATx9pcs(1bank)	Now
			HYM71V16755AT8M	-P -S	10 10	900 / 18 900 / 18	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820ATx9pcs(1bank) PCB height : 1.25 inch,4 Layer PCB	Now
			HYM71V16735AT8M	-K -H	7.5 7.5	1080 / 18 990 / 18	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820HCTx9pcs(1bank) PCB height : 1.25 inch,4 Layer PCB	Now
			HYM71V16755HCT8	-P -S	10 10	900 / 7.2 900 / 7.2	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820HCTx9pcs(1bank)	Now
			HYM71V16735HCT8	-K -H	7.5 7.5	990 / 7.2 990 / 7.2	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820HCTx9pcs(1bank)	Now
			HYM71V16755HCT8M	-P -S	10 10	900 / 7.2 900 / 7.2	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820HCTx9pcs(1bank) PCB height : 1.25 inch,4 Layer PCB	Now
			HYM71V16735HCT8M	-K -H	7.5 7.5	990 / 7.2 990 / 7.2	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V1298020TCx16pcs(2banks) PCB height : 1.25 inch,4 Layer PCB	Now
		32Mx72 (256MB)	HYM71V32755AT8	-P -S	10 10	1260 / 36 1260 / 36	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820ATx18pcs(2banks)	Now

SDRAM Module

TYPE		CONFIG. (Capacity)	PART NUMBER	SUFFIX	FEATURES CYCLE (ns)	FEATURES ACT./STD-BY (mA)	REMARKS	SAMPLE AVAILABLE
SDR MODULE	168pin Unbuffered DIMM (ECC)	32Mx72 (256MB)	HYM71V32735AT8	-K -H	7.5 7.5	1350 / 36 1350 / 36	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820ATx18pcs(2banks)	Now
			HYM71V32755AT8M	-P -S	10 10	1260 / 36 1260 / 36	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820ATx18pcs(2banks) PCB height : 1.25 inch,4 Layer PCB	Now
			HYM71V32735AT8M	-K -H	7.5 7.5	1510 / 36 1350 / 36	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820HCTx18pcs(2banks) PCB height : 1.25 inch,4 Layer PCB	Now
			HYM71V32755HCT8	-P -S	10 10	1260 / 36 1260 / 36	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820HCTx18pcs(2banks)	Now
			HYM71V32735HCT8	-K -H	7.5 7.5	1350 / 36 1350 / 36	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820HCTx18pcs(2banks)	Now
			HYM71V32755HCT8M	-P -S	10 10	1260 / 36 1260 / 36	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820HCTx18pcs(2banks) PCB height : 1.25 inch,4 Layer PCB	Now
			HYM71V32735HCT8M	-K -H	7.5 7.5	1350 / 36 1350 / 36	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820HCTx18pcs(2banks) PCB height : 1.25 inch,4 Layer PCB	Now
			HYM72V32756T8	- S	10	900 / 36	256Mb 1st Generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V56820T x 8pcs (1Bank)	Now
			HYM72V32736T8	- H	7.5	990 / 36	256Mb 1st Generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V56820T x 8pcs (1Bank)	Now
			HYM72V32736AT8 HYM72V32756AT8 HYM72V32756AT8	- H - P - S	7.5 10 10	TBD	256Mb 2nd Generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V56820AT x 8pcs (1Bank)	3Q
		64Mx72 (512MB)	HYM72V64756T8 HYM72V64736T8	- S - H	10 7.5	1170 / 72 1350 / 90	256Mb 1st Generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V56820T x 18pcs (2bank)	Now
			HYM72V64736AT8 HYM72V64756AT8 HYM72V64756AT8	- H - P - S	7.5 10 10	TBD	256Mb 2nd Generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V56820AT x 18pcs (2Bank)	3Q
			HYM72V64736HDT8 HYM72V64756HDT8 HYM72V64756HDT8	- H - P - S	7.5 10 10	TBD	256Mb D Version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V56820HDT x 18pcs (2Bank)	3Q
	168pin Reg.DIMM	8Mx72 (64MB)	HYM7V75AC801BTHG	- 10P - 10S	10 10	950 / 258 950 / 258	64Mb 4th generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V658020BTC x 9pcs(1Bank) RCC TYPE	Now
			HYM7V73AC801BTHG	- 75	7.5	1130 / 258	64Mb 4th generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V658020BTC x 9pcs(1Bank)	Now
			GMM2739230EPTG	- 7K - 7J	10 10	720 / 10 720 / 10	64Mb E version based VDD = 3.3V +/- 0.3V (LVTTL) GM72V66841ET x 9pcs(1Bank) JEDEC TYPE	Now
			HYM76V8S755HGT8	- P - S	10 10	950 / 258 950 / 258	64Mb G version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V64820HGT x 9pcs(1Bank) RCC TYPE	Now
			HYM76V8C735HGT8	- K - H	7.5 7.5	1130 / 258 1130 / 258	64Mb G version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V64820HGT x 9pcs(1Bank) RCC TYPE	Now

SDRAM Module

TYPE		CONFIG. (Capacity)	PART NUMBER	SUFFIX	FEATURES		REMARKS	SAMPLE AVAILABLE
					CYCLE (ns)	ACT./STD-BY (mA)		
SDR MODULE	168pin Reg.DIMM	16Mx72 (128MB)	HYM76V16S755HGT4	- P - S	10 10	1580 / 276 1580 / 276	64Mb G version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V64420HGT x 18pcs(2Bank) RCC TYPE	Now
			HYM76V16C735HGT4	- K - H	7.5 7.5	1940 / 276 1940 / 276	64Mb G version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V64420HGT x 18pcs(2Bank) RCC TYPE	Now
			GMM27317230ATG	-7K -7J	10 10	1100 / 20 1100 / 20	128Mbit A version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V1298020TCx9pcs(1bank)	Now
			HYM71V16C755AT8	-P -S	10 10	1200 / 430 1200 / 430	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820ATx9pcs(1bank) , Intel Type	Now
			HYM71V16C735AT8	-K -H	7.5 7.5	1400 / 430 1400 / 430	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820ATx9pcs(1bank), RCC Type	Now
			HYM71V16C735HCT8M	-K -H	7.5 7.5	TBD TBD	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820HCTx9pcs(1bank), RCC Type PCB height : 1.125 inch	Now
			HYM71V16C755HCT8	-P -S	10 10	1200/430 1200/430	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820ATx9pcs(1bank), RCC Type	Now
			HYM71V16C735HCT8	-K -H	7.5 7.5	1400/430 1400/430	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820HCTx9pcs(1bank), RCC Type	Now
		32Mx72 (256MB)	HYM71V32S755AT4	-P -S	10 10	2200/ 276 2200/ 276	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28420ATx18pcs(1bank), RCC Type	Now
			HYM71V32C735AT4	-K -H	7.5 7.5	2400 / 276 2400 / 276	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28420ATx18pcs(1bank), RCC Type	Now
			HYM71V32S755AT4M	-8 -P -S	8 10 10	2200/ 276 2200/ 276 2200/ 276	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28420ATx18pcs(1bank), Intel Type PCB height : 1.7 inch,4 Layer PCB	Now
			HYM71V32S755AT4	-8 -P -S	8 10 10	2200 / 276 2200 / 276 2200 / 276	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28420ATx18pcs(1bank), Intel Type	Now
			HYM71V32C755HCT4	-P -S	10 10	2200/276 2200/276	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28420HCTx18pcs(1bank), RCC Type	Now
			HYM71V32S755HCT4	-P -S	10 10	2200/276 2200/276	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28420HCTx18pcs(1bank), Intel Type	Now
			HYM71V32D755HCT4	-P -S	10 10	2200/276 2200/276	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28420HCTx18pcs(1bank), Jedec Type	Now
			HYM71V32C735HCT4	-K -H	7.5 7.5	2400/276 2400/276	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28420HCTx18pcs(1bank), RCC Type	Now
			HYM72V32C736T8 HYM72V32S756T8	- H - S	7.5 10	1400 / 430 1230 / 19.5	256Mb 1st Generation based VDD = 3.3 +/- 0.3V (LVTTL) HY57V56820T x 9pcs (1Bank) RCC(PC133)/ INTEL(PC100) TYPE	Now
			HYM72V32C736AT8 HYM72V32S756AT8 HYM72V32S756AT8	- H - P - S	7.5 10 10	TBD TBD TBD	256Mb 2nd Generation based VDD = 3.3 +/- 0.3V (LVTTL) HY57V56820AT x 9pcs (1Bank) RCC(PC133)/ INTEL(PC100) TYPE	3Q

SDRAM Module

TYPE		CONFIG. (Capacity)	PART NUMBER	SUFFIX	FEATURES CYCLE (ns)	FEATURES ACT./STD-BY (mA)	REMARKS	SAMPLE AVAILABLE
SDR MODULE	168pin Reg.DIMM	32Mx72 (256MB)	HYM72V32C736HDT8 HYM72V32S756HDT8 HYM72V32S756HDT8	- H - P - S	7.5 10 10	TBD TBD TBD	256Mb D Version based VDD = 3.3 +/- 0.3V (LVTTL) HY57V56820HDT x 9pcs (1Bank) RCD(PC133)/ INTEL(PC100) TYPE	3Q
		64Mx72 (512MB)	HYM72V64C736T4 HYM72V64S756T4	- H - S	7.5 10	2400 / 440 2360 / 38	256Mb 1st Generation based VDD = 3.3 +/- 0.3V (LVTTL) HY57V56420T x 18pcs (1Bank) RCD(PC133)/ INTEL(PC100) TYPE	Now
			HYM72V64C736AT4 HYM72V64S756AT4 HYM72V64S756AT4	- H - P - S	7.5 10 10	TBD TBD TBD	256Mb 2nd Generation based VDD = 3.3 +/- 0.3V (LVTTL) HY57V56420AT x 18pcs (1Bank) RCD(PC133)/ INTEL(PC100) TYPE	3Q
			HYM72V64C736HDT4 HYM72V64S756HDT4 HYM72V64S756HDT4	- H - P - S	7.5 10 10	TBD TBD TBD	256Mb D Version based VDD = 3.3 +/- 0.3V (LVTTL) HY57V56420HDT x 18pcs (1Bank) RCD(PC133)/ INTEL(PC100) TYPE	3Q
			HYM72V64C736K8M	- H	7.5	TBD	256Mb 1st Generation based VDD = 3.3 +/- 0.3V (LVTTL) (32Mx8)*2 Stack x 9pcs RCD(PC133) PCB Height : 1.125 inch	Now
		128Mx72 (1GB)	HYM72V12C736K4 HYM72V12C756K4	- H - S	7.5 10	2760 / 550 2300 / 180	256Mb 1st Generation based VDD = 3.3 +/- 0.3V (LVTTL) (64Mx4)*2 Stack x 18pcs RCD(PC133)	Now
			HYM72V12C736AK4 HYM72V12C756AK4	- H - P - S	7.5 10 10	TBD TBD TBD	256Mb 2nd Generation based VDD = 3.3 +/- 0.3V (LVTTL) (64Mx4)*2 Stack x 18pcs RCD(PC133)	4Q
			HYM72V12C736HDK4 HYM72V12C756HDK4	- H - P - S	7.5 10 10	TBD TBD TBD	256Mb D Version based VDD = 3.3 +/- 0.3V (LVTTL) (64Mx4)*2 Stack x 18pcs RCD(PC133)	4Q
	144pin SO-DIMM	4Mx64 (32MB)	HYM76V4M655HGT6	- P - S	10 10	280 / 8 280 / 8	64Mb G version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V641620HGT x 4pcs(1Bank)	Now
			HYM76V4M635HGT6	- K - H	7.5 7.5	320 / 8 320 / 8	64Mb G version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V641620HGT x 4pcs(1Bank)	Now
		8Mx64 (64MB)	HYM7V65801B(L)TQG	- 10P - 10S	10 10	400 / 16(4) 400 / 16(4)	64Mb 4th generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V651620B(L)TC x 8pcs(2Bank) (): Low Power Mode	Now
			HYM76V8M655HGT6	- P - S	10 10	400 / 16 400 / 16	64Mb G version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V641620HGT x 8pcs(2Bank)	Now
			HYM76V8M635HGT6	- K - H	7.5 7.5	480 / 16 480 / 16	64Mb G version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V641620HGT x 8pcs(2Bank)	Now
			HYM7V75A801B(L)TZG	- 10P - 10S	10 10	630/ 18(4.5) 630 / 18(4.5)	64Mb 4th generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V658020B(L)TC x 9pcs(1Bank) (): Low Power Mode	Now
			HYM71V8M655A(L)T6	-P -S	10 10	400 / 8(3.2) 400 / 8(3.2)	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V281620A(L)Tx4pcs(1bank) (): Low Power Mode	Now
			HYM71V8M635A(L)T6	-K -H	7.5 7.5	400 / 8(3.2) 400 / 8(3.2)	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V281620A(L)Tx4pcs(1bank) (): Low Power Mode	Now

SDRAM Module

TYPE		CONFIG. (Capacity)	PART NUMBER	SUFFIX	FEATURES		REMARKS	SAMPLE AVAILABLE
					CYCLE (ns)	ACT./STD-BY (mA)		
SDR MODULE	144pin SO-DIMM	8Mx64 (64MB)	HYM71V8M655A(L)TU6	-P -S	10 10	400 / 8(3.2) 400 / 8(3.2)	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V281620A(L)Tx4pcs(1bank) (): Low Power Mode	Now
			HYM71V8M655HC(L)T6	-P -S	10 10	480/18(3.2) 480/18(3.2)	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V281620HC(L)Tx4pcs(1bank) (): Low Power Mode	Now
			HYM71V8M655HC(L)TU6	-P -S	10 10	480/18(3.2) 480/18(3.2)	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V281620HC(L)Tx4pcs(1bank) (): Low Power Mode	Now
			HYM71V8M635HC(L)T6	-K -H	7.5 7.5	480/18(3.2) 480/18(3.2)	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V281620HC(L)Tx4pcs(1bank) (): Low Power Mode	Now
		16Mx64 (128MB)	HYM71V16M655A(L)T6	-P -S	10 10	560/16(6.4) 560/16(6.4)	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V281620A(L)Tx8pcs(2banks) (): Low Power Mode	Now
			HYM71V16M635A(L)T6	-K -H	7.5 7.5	600/16(6.4) 600/16(6.4)	128Mbit 3rd generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V281620A(L)Tx8pcs(2banks) (): Low Power Mode	Now
			HYM71V16M655HC(L)T6	-P -S	10 10	960/16(6.4) 960/16(6.4)	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V281620HC(L)Tx8pcs(2banks) (): Low Power Mode	Now
			HYM71V16M635HC(L)T6	-K -H	7.5 7.5	960/16(6.4) 960/16(6.4)	128Mbit C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V281620HC(L)Tx8pcs(2banks) (): Low Power Mode	Now
			HYM72V16M636T6 HYM72V16M656T6	- H - S	7.5 10	440/ 8 440/ 8	256Mb 1st Generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V561620T x 4pcs (1Bank)	Now
			HYM72V16M636A(L)T6 HYM72V16M656A(L)T6 HYM72V16M656A(L)T6	- H - P - S	7.5 10 10	TBD TBD TBD	256Mb 2nd Generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V561620A(L)T x 4pcs (1Bank) (): Low Power Mode	3Q
			HYM72V16M636HD(L)T6 HYM72V16M656HD(L)T6 HYM72V16M656HD(L)T6	- H - P - S	7.5 10 10	TBD TBD TBD	256Mb D Version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V561620HD(L)T x 4pcs (1Bank) (): Low Power Mode	3Q
		32Mx64 (256MB)	HYM71V32M655HC(L)Y8	-P -S	10 10	1120/32(12.8) 1120/32(12.8)	128Mb C version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V28820HC(L)Yx16pcs(2Bank) (): Low Power Mode	Now
			HYM72V32M636(L)T6 HYM72V32M656(L)T6	- H - S	7.5 10	600/ 16 600/ 16	256Mb 1st Generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V561620T x 8pcs (2Bank)	Now
			HYM72V32M636A(L)T6 HYM72V32M656A(L)T6 HYM72V32M656A(L)T6	- H - P - S	7.5 10 10	TBD TBD TBD	256Mb 2nd Generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V561620A(L)T x 8pcs (2Bank) (): Low Power Mode	3Q
			HYM72V32M636HD(L)T6 HYM72V32M656HD(L)T6 HYM72V32M656HD(L)T6	- H - P - S	7.5 10 10	TBD TBD TBD	256Mb D Version based VDD = 3.3V +/- 0.3V (LVTTL) HY57V561620HD(L)T x 8pcs (2Bank) (): Low Power Mode	3Q
	132pin AIMM	1Mx32 (4MB)	HYM4V33100DTYG	- 75	7.5	220 / 4	16Mb 5th generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V161610DTC x 2pcs(1Bank)	Now
			HYM4V33100BTWG	- 75	7.5	220 / 4	64Mb 4th generation based VDD = 3.3V +/- 0.3V (LVTTL) HY57V653220BTC x 1pcs(1Bank)	Now

DDR SDRAM Module

TYPE		CONFIG. (Capacity)	PART NUMBER	SUFFIX	FEATURES CYCLE (ns)	FEATURES ACT./STD-BY (mA)	REMARKS	SAMPLE AVAILABLE
DDR MODULE	184pin Un-buffered DIMM	8Mx64 (64MB)	HYMD186456	- H	7.5	600 / 8	128Mb 2nd Generation based	Now
				- L	10	560 / 8	VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2)	
							HY5DU281622T x 4pcs (1Bank)	
							PCB Height : 1.25 inch	
			HYMD18645A6	- K	7.5	TBD	128Mb 3rd Generation based	Now
				- H	7.5	TBD	VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2)	
				- L	10	TBD	HY5DU281622AT x 4pcs (1Bank)	
							PCB Height : 1.25 inch	
		16Mx64 (128MB)	HYMD1166458	- H	7.5	1120 / 16	128Mb 2nd Generation based	Now
				- L	10	1040 / 16	VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2)	
							HY5DU28822T x 8pcs (1Bank)	
							PCB Height : 1.25 inch	
			HYMD116645A8	- K	7.5	TBD	128Mb 3rd Generation based	Now
				- H	7.5	TBD	VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2)	
				- L	10	TBD	HY5DU28822AT x 8pcs (1Bank)	
							PCB Height : 1.25 inch	
			HYMD2166466	- K	7.5	480 / 12	256Mb 2nd Generation based	4Q
				- H	7.5	480 / 12	VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2)	
				- L	10	480 / 12	HY5DU561622T x 4pcs (1Bank)	
							PCB Height : 1.25 inch	
		16Mx72 (128MB) ECC	HYMD1167258	- H	7.5	1260 / 18	128Mb 2nd Generation based	Now
				- L	10	1170 / 18	VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2)	
							HY5DU28822T x 9pcs (1Bank)	
							PCB Height : 1.25 inch	
			HYMD116725A8	- K	7.5	TBD	128Mb 3rd Generation based	Now
				- H	7.5	TBD	VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2)	
				- L	10	TBD	HY5DU28822AT x 9pcs (1Bank)	
							PCB Height : 1.25 inch	
		32Mx64 (256MB)	HYMD1326458	- H	7.5	2240 / 32	128Mb 2nd Generation based	Now
				- L	10	2080 / 32	VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2)	
							HY5DU28822T x 16pcs (2Bank)	
							PCB Height : 1.25 inch	
			HYMD132645A8	- K	7.5	TBD	128Mb 3rd Generation based	Now
				- H	7.5	TBD	VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2)	
				- L	10	TBD	HY5DU28822AT x 16pcs (2Bank)	
							PCB Height : 1.25 inch	
			HYMD2326468	- K	7.5	960 / 24	256Mb 2nd Generation based	4Q
				- H	7.5	960 / 24	VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2)	
				- L	10	880 / 24	HY5DU56822T x 8pcs (1Bank)	
							PCB Height : 1.25 inch	
		32Mx72 (256MB) ECC	HYMD1327258	- H	7.5	2520 / 36	128Mb 2nd Generation based	Now
				- L	10	2340 / 36	VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2)	
							HY5DU28822T x 18pcs (2Bank)	
							PCB Height : 1.25 inch	
			HYMD132725A8	- K	7.5	TBD	128Mb 3rd Generation based	Now
				- H	7.5	TBD	VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2)	
				- L	10	TBD	HY5DU28822AT x 18pcs (2Bank)	
							PCB Height : 1.25 inch	

DDR SDRAM Module

TYPE		CONFIG. (Capacity)	PART NUMBER	SUFFIX	FEATURES		REMARKS	SAMPLE AVAILABLE
					CYCLE (ns)	ACT./STD-BY (mA)		
DDR MODULE	184pin Un-buffered DIMM	32Mx72 (256MB) ECC	HYMD2327268	- K	7.5	1080 / 27	256Mb 2nd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU56822T x 9pcs (1Bank) PCB Height : 1.25 inch	4Q
				- H	7.5	1080 / 27		
				- L	10	990 / 27		
		64Mx64 (512MB)	HYMD2646468	- K	7.5	1360 / 48	256Mb 2nd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU56822T x 16pcs (2Bank) PCB Height : 1.25 inch	4Q
				- H	7.5	1360 / 48		
				- L	10	1280 / 48		
		64Mx72 (512MB) ECC	HYMD2647268	- K	7.5	1530 / 54	256Mb 2nd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU56822T x 18pcs (2Bank) PCB Height : 1.25 inch	4Q
				- H	7.5	1530 / 54		
				- L	10	1440 / 54		
	184pin Registered DIMM	16Mx72 (128MB)	HYMD116G7258	- H	7.5	1260 / 18	128Mb 2nd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU28822T x 9pcs (1Bank) PCB Height : 1.7 inch	Now
				- L	10	1170 / 18		
			HYMD116G725A8	- K	7.5	TBD	128Mb 3rd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU28822AT x 9pcs (1Bank) PCB Height : 1.7 inch	Now
				- H	7.5	TBD		
				- L	10	TBD		
		32Mx72 (256MB)	HYMD132G7254	- H	7.5	2340 / 36	128Mb 2nd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU28422T x 18pcs (1Bank) PCB Height : 1.7 inch	Now
				- L	10	2160 / 36		
			HYMD132G7258	- H	7.5	2520 / 36	128Mb 2nd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU28822T x 18pcs (2Bank) PCB Height : 1.7 inch	Now
				- L	10	2340 / 36		
			HYMD132G725A4	- K	7.5	TBD	128Mb 3rd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU28422AT x 18pcs (1Bank) PCB Height : 1.7 inch	Now
				- H	7.5	TBD		
				- L	10	TBD		
			HYMD132G725A8	- K	7.5	TBD	128Mb 3rd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU28822AT x 18pcs (2Bank) PCB Height : 1.7 inch	Now
				- H	7.5	TBD		
				- L	10	TBD		
			HYMD232G7268	- K	7.5	TBD	256Mb 2nd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU56822T x 9pcs (1Bank) PCB Height : 1.7 inch	4Q
				- H	7.5	TBD		
				- L	10	TBD		
		64Mx72 (512MB)	HYMD264G7268	- K	7.5	TBD	256Mb 2nd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU56822T x 18pcs (2Bank) PCB Height : 1.7 inch	4Q
				- H	7.5	TBD		
				- L	10	TBD		

DDR SDRAM Module

TYPE		CONFIG. (Capacity)	PART NUMBER	SUFFIX	FEATURES		REMARKS	SAMPLE AVAILABLE
					CYCLE (ns)	ACT./STD-BY (mA)		
DDR MODULE	184pin Registered DIMM	64Mx72 (512MB)	HYMD264G7264	- K - H - L	7.5 7.5 10	TBD TBD TBD	256Mb 2nd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU56422T x 18pcs (1Bank) PCB Height : 1.7 inch	4Q
		128Mx72 (1GB)	HYMD212G726K4 (Stack base)	- K - H - L	7.5 7.5 10	TBD TBD TBD	256Mb 2nd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU28422T x 36pcs (1Bank) PCB Height : 1.7 inch	4Q
	200pin SO-DIMM	8Mx64 (64MB)	HYMD18M6456	- H - L	7.5 10	570 / 6 440 / 6	128Mb 2nd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU281622T x 4pcs (1Bank) PCB Height : 1.25 inch	Now
			HYMD18M645A6	- K - H - L	7.5 7.5 10	TBD TBD TBD	128Mb 3rd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU281622AT x 4pcs (1Bank) PCB Height : 1.25 inch	Now
		16Mx64 (128MB)	HYMD116M6456	- H - L	7.5 10	540 / 9 420 / 9	128Mb 2nd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU281622T x 8pcs (2Bank) PCB Height : 1.25 inch	Now
			HYMD116M6458	- H - L	7.5 10	900 / 9 700 / 9	128Mb 2nd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU28822T x 8pcs (1Bank) PCB Height : 1.25 inch	Now
			HYMD116M645A6	- K - H - L	7.5 7.5 10	TBD TBD TBD	128Mb 3rd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU281622AT x 8pcs (2Bank) PCB Height : 1.25 inch	Now
			HYMD116M645A8	- K - H - L	7.5 7.5 10	TBD TBD TBD	128Mb 3rd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU28822AT x 8pcs (1Bank) PCB Height : 1.25 inch	Now
			HYMD216M6466	- K - H - L	7.5 7.5 10	TBD TBD TBD	256Mb 2nd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU561622T x 4pcs (1Bank) PCB Height : 1.25 inch	4Q
		32Mx64 (256MB)	HYMD232M6466	- K - H - L	7.5 7.5 10	TBD TBD TBD	256Mb 2nd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU561622T x 8pcs (2Bank) PCB Height : 1.25 inch	4Q
			HYMD232M6468	- K - H - L	7.5 7.5 10	TBD TBD TBD	256Mb 2nd Generation based VDD/VDDQ = 2.5 V +/- 0.2 V (SSTL-2) HY5DU56822T x 8pcs (1Bank) PCB Height : 1.25 inch	4Q

Rambus RIMM Module

TYPE		CONFIG. (Capacity)	PART NUMBER	SUFFIX	FEATURES		REMARKS	SAMPLE AVAILABLE
					CYCLE (ns)	ACT./STD-BY (mA)		
DRD MODULE	184-pin RIMM	32Mx16 (64MB)	HYMR23216H	-653	600MHz	TBD	256Mb A-ver based	3Q
				-745	711MHz	TBD	2.5V+/- 5% power supply	
				-845	800MHz	TBD	HY5R256HCx2pcs	
				-840	800MHz	TBD	tRAC= 53ns,45ns,40ns	
		32Mx18 (64MB)	HYMR23218H	-653	600MHz	TBD	288Mb A-ver based	3Q
				-745	711MHz	TBD	2.5V+/- 5% power supply	
				-845	800MHz	TBD	HY5R288HCx2pcs	
				-840	800MHz	TBD	tRAC= 53ns,45ns,40ns	
		64Mx16 (128MB)	HYMR16416H	-653	600MHz	1616 / 527	128 A-ver based	Now
				-745	711MHz	1811 / 603	2.5V+/- 5% power supply	
							HY5R128HCx8pcs	
							tRAC= 53ns,45ns,40ns	
		64Mx18 (128MB)	HYMR16418H	-653	600MHz	1655 / 500	144Mb A-ver based	Now
				-745	711MHz	1838 / 572	2.5V+/- 5% power supply	
							HY5R144HCx8pcs	
							tRAC= 53ns,45ns,40ns	
		64Mx16 (128MB)	HYMR26416H	-653	600MHz	910 / 593	256Mb A-ver based	3Q
				-745	711MHz	1100 / 698	2.5V+/- 5% power supply	
				-845	800MHz	1180 / 751	HY5R256HCx4pcs	
				-840	800MHz	1180 / 751	tRAC= 53ns,45ns,40ns	
		64Mx18 (128MB)	HYMR26418H	-653	600MHz	910 / 593	288Mb A-ver based	3Q
				-745	711MHz	1100 / 698	2.5V+/- 5% power supply	
				-845	800MHz	1180 / 751	HY5R288HCx4pcs	
				-840	800MHz	1180 / 751	tRAC= 53ns,45ns,40ns	
		128Mx16 (256MB)	HYMR212816H	-653	600MHz	1390 / 609	256Mb A-ver based	3Q
				-745	711MHz	1700 / 714	2.5V+/- 5% power supply	
				-845	800MHz	1820 / 767	HY5R256HCx8pcs	
				-840	800MHz	1820 / 767	tRAC= 53ns,45ns,40ns	
		128Mx18 (256MB)	HYMR212818H	-653	600MHz	1390 / 609	288Mb A-ver based	3Q
				-745	711MHz	1700 / 714	2.5V+/- 5% power supply	
				-845	800MHz	1820 / 767	HY5R288HCx8pcs	
				-840	800MHz	1820 / 767	tRAC= 53ns,45ns,40ns	
		256Mx16 (512MB)	HYMR225616H	-653	600MHz	2350 / 641	256Mb A-ver based	3Q
				-745	711MHz	2900 / 746	2.5V+/- 5% power supply	
				-845	800MHz	3100 / 798	HY5R256HCx16pcs	
				-840	800MHz	3100 / 798	tRAC= 53ns,45ns,40ns	
		256Mx18 (512MB)	HYMR225618H	-653	600MHz	2350 / 641	288Mb A-ver based	3Q
				-745	711MHz	2900 / 746	2.5V+/- 5% power supply	
				-845	800MHz	3100 / 798	HY5R288HCx16pcs	
				-840	800MHz	3100 / 798	tRAC= 53ns,45ns,40ns	

SRAM

TECH	DENSITY	ORG.	VOLTAGE	PART NUMBER	PACKAGE TYPE	FEATURES				REMARK	SAMPLE AVAILABLE
						SPEED (ns)	ICC1 (mA)	ISB1 (uA) LL	ISB1 (uA) SL		
TFT	256K	32Kx8	5.0V	GM76C256C	PDIP	55	70	30		4th Generation	Now
			3.3V	GM76V256C	SOP	85	35	15			
			3.0V	GM76U256C	TSOP-I	100	30	15			
			5.0V	HY62CT08081E	PDIP	55	50	20		6th Generation	Now
			3.3V	HY62VT08081E	SOP	70	30	8			
			3.0V	HY62UT08081E	TSOP-I	70	30	8			
	1M	128Kx8	5.0V	HY628100B	SOP	55	50	30		3rd Generation	Now
			3.3V	HY62V8100B	TSOP-I	70	35	15			
			3.0V	HY62U8100B	sTSOP	70	30	15			
	2M	256Kx8	3.3V	HY62V8200B	TSOP-I	70	35	25		3rd Generation	Now
			3.0V	HY62U8200B	sTSOP	70	30	25			
	4M	512Kx8	5.0V	HY628400A	SOP	55	60	50		2nd Generation	Now
			3.3V	HY62V8400A	TSOP-II	70	40	30			
			3.0V	HY62U8400A		70	35	30			
FCMOS	1M	64Kx16	3.0V	HY62UF16101C	FBGA	55	45	5	1	4th Generation	Now
			2.5V	HY62LF16101C		70	30	3	1		
			1.8V	HY62SF16101C		85	25	2	1		
	2M	128Kx16	3.0V	HY62UF16201A	FBGA	55	45	10	2	2nd Generation	Now
			2.5V	HY62LF16201A		70	30	5	2		
			1.8V	HY62SF16201A		85	20	3	1		
	4M	512Kx8	3.3V	HY62VF08401C	sTSOP	55	45	20	4	4th Generation	Now
			3.0V	HY62UF08401C		55	40	15	4		
		256Kx16	3.0V	HY62UF16403A	uBGA	55	50	15	4	2nd Generation, 1CS	Now
			1.8V	HY62SF16403A		85	20	10	2		
			3.0V	HY62UF16404C	uBGA	55	50	15	4	4th Generation, 1CS	Now
			2.5V	HY62LF16404C		70	30	12	4		
			1.8V	HY62SF16404C		85	20	10	2		
			3.0V	HY62UF16406C		55	50	15	4	4th Generation, 2CS	Now
			2.5V	HY62LF16406C		70	30	12	4		
			1.8V	HY62SF16406C		85	20	10	2		
			3.0V	HY62UF16404D	FBGA	55	40	12	4	5th Generation, 1CS	3Q'01
			2.5V	HY62LF16404D		70	25	10	3		
			1.8V	HY62SF16404D		70	20	12	4		
			3.0V	HY62UF16406D		55	40	12	4	5th Generation, 2CS	
			2.5V	HY62LF16406D		70	25	10	3		
			1.8V	HY62SF16406D		70	20	12	4		
	8M	512Kx16	3.0V	HY62UF16804A	uBGA	55	50	40	8	2nd Generation, 1CS	Now
			2.5V	HY62LF16804A		70	30	30	8		
			1.8V	HY62SF16804A		70	25	25	8		
			3.0V	HY62UF16806A		55	50	40	8	2nd Generation, 2CS	
			2.5V	HY62LF16806A		70	30	30	8		
			1.8V	HY62SF16806A		70	25	25	8		
1T1C SRAM	16M	1Mx16	3.0V	HY62UD16162M	FBGA	85	30	100		Idpd = 10uA	1Q'02
			2.5V	HY62LD16162M		85	30	100			
	32M	2Mx16	3.0V	HY62UD16322M	FBGA	85	30	100			
			2.5V	HY62LD16322M		85	30	100			

FLASH MEMORY

TYPE	DENSITY	ORG.	PACKAGE	VOLT.	PART NUMBER	FEATURES					REMARKS	SAMPLE AVAILABLE
						SPEED (ns)	BANK	ARCHITECTURE (Sector type)	ICC(mA) BYTE/WORD	ISB1(uA)		
F	2M	256Kx8	32pin TSOP	5.0V	HY29F002BT	45	Single	Bottom Boot	30	5	1st Generation Vcc: 4.5~5.5V	Now
L						55			30	5		
A						70			30	5		
S						90			30	5		
H						120			30	5		
					HY29F002TT	45	Single	Top Boot	30	5	1st Generation Vcc: 4.5~5.5V	Now
						55			30	5		
						70			30	5		
						90			30	5		
						120			30	5		
			32pin PLCC	5.0V	HY29F002BC	45	Single	Bottom Boot	30	5	1st Generation Vcc: 4.5~5.5V	Now
						55			30	5		
						70			30	5		
						90			30	5		
						120			30	5		
					HY29F002TC	45	Single	Top Boot	30	5	1st Generation Vcc: 4.5~5.5V	Now
						55			30	5		
						70			30	5		
						90			30	5		
						120			30	5		
	4M	512Kx8	32pin TSOP	5.0V	HY29F040AT	55	Single	Uniform	30	5	2nd Generation Vcc: 4.5~5.5V	Now
						70			30	5		
						90			30	5		
						120			30	5		
						150			30	5		
			32pin PLCC	5.0V	HY29F040AC	55	Single	Uniform	30	5	2nd Generation Vcc: 4.5~5.5V	Now
						70			30	5		
						90			30	5		
						120			30	5		
						150			30	5		
		512Kx8/ 256Kx16	48pin TSOP	5.0V	HY29F400BT	45	Single	Bottom Boot	40/50	5	1st Generation Vcc: 4.5~5.5V	Now
						55			40/50	5		
						70			40/50	5		
						90			40/50	5		
					HY29F400TT	45	Single	Top Boot	40/50	5	1st Generation Vcc: 4.5~5.5V	Now
						55			40/50	5		
						70			40/50	5		
						90			40/50	5		
			44pin SOP	5.0V	HY29F400BG	45	Single	Bottom Boot	40/50	5	1st Generation Vcc: 4.5~5.5V	Now
						55			40/50	5		
						70			40/50	5		
						90			40/50	5		
					HY29F400TG	45	Single	Top Boot	40/50	5	1st Generation Vcc: 4.5~5.5V	Now
						55			40/50	5		
						70			40/50	5		
						90			40/50	5		
	8M	1Mx8	40pin TSOP	5.0V	HY29F080T	70	Single	Uniform	40	5	1st Generation Vcc: 4.5~5.5V	Now
						90			40	5		
						120			40	5		
			44pin SOP	5.0V	HY29F080G	70	Single	Uniform	40	5	1st Generation Vcc: 4.5~5.5V	Now
						90			40	5		
						120			40	5		
		1Mx8/ 512Kx16	48pin TSOP	5.0V	HY29F800BT	55	Single	Bottom Boot	40/50	5	1st Generation Vcc: 4.5~5.5V	Now
						70			40/50	5		
						90			40/50	5		
						120			40/50	5		
					HY29F800TT	55	Single	Top Boot	40/50	5	1st Generation Vcc: 4.5~5.5V	Now
						70			40/50	5		
						90			40/50	5		
						120			40/50	5		
			44pin SOP	5.0V	HY29F800BG	55	Single	Bottom Boot	40/50	5	1st Generation Vcc: 4.5~5.5V	Now
						70			40/50	5		
						90			40/50	5		
						120			40/50	5		
					HY29F800TG	55	Single	Top Boot	40/50	5	1st Generation Vcc: 4.5~5.5V	Now
						70			40/50	5		
						90			40/50	5		
						120			40/50	5		

FLASH MEMORY

TYPE	DENSITY	ORG.	PACKAGE	VOLT.	PART NUMBER	FEATURES					REMARKS	SAMPLE AVAILABLE
						SPEED (ns)	BANK	ARCHITECTURE (Sector type)	ICC(mA) R/T/E/WORD	ISB1(uA)		
F L A S H	16M	2Mx8/ 1Mx16	48pin TSOP	3.0V	HY29LV160BT	70 90 120	Single	Bottom Boot	4/4 4/4 4/4	5 5 5	1st Generation Vcc: 2.7~3.6V (In the case of 70ns, only available voltage is 3.0~3.6V) Industrial Temp (-40C ~85C).	Now
					HY29LV160TT	70 90 120	Single	Top Boot	4/4 4/4 4/4	5 5 5	1st Generation Vcc: 2.7~3.6V (In the case of 70ns, only available voltage is 3.0~3.6V) Industrial Temp (-40C ~85C)	Now
			48pin FBGA	3.0V	HY29LV160BF	70 90 120	Single	Bottom Boot	4/4 4/4 4/4	5 5 5	1st Generation Vcc: 2.7~3.6V Industrial Temp(-40C ~85C)	Now
					HY29LV160TF	70 90 120	Single	Top Boot	4/4 4/4 4/4	5 5 5	1st Generation Vcc: 2.7~3.6V Industrial Temp(-40C ~85C)	Now
			48pin TSOP	3.0V	HY29DL162BT	70 90 120	Dual	Bottom Boot	10/10 10/10 10/10	5 5 5	1st Generation, Vcc: 2.7~3.6V, Industrial Temp(-40C ~85C) Bank Size -Bank1:8x8KB, 3x64KB -Bank2:28x64KB	3Q
					HY29DL162TT	70 90 120	Dual	Top Boot	10/10 10/10 10/10	0.2 0.2 0.2	1st Generation, Vcc: 2.7~3.6V, Industrial Temp(-40C ~85C) Bank Size -Bank1:8x8KB, 3x64KB -Bank2:28x64KB	3Q
					HY29DL163BT	70 90 120	Dual	Bottom Boot	10/10 10/10 10/10	0.2 0.2 0.2	1st Generation, Vcc: 2.7~3.6V, Industrial Temp(-40C ~85C) Bank Size -Bank1:8x8KB, 7x64KB -Bank2:24x64KB	Now
					HY29DL163TT	70 90 120	Dual	Top Boot	10/10 10/10 10/10	0.2 0.2 0.2	1st Generation, Vcc: 2.7~3.6V, Industrial Temp(-40C ~85C) Bank Size -Bank1:8x8KB, 7x64KB -Bank2:24x64KB	Now
			48pin FBGA	3.0V	HY29DL162BF	70 90 120	Dual	Bottom Boot	10/10 10/10 10/10	0.2 0.2 0.2	1st Generation, Vcc: 2.7~3.6V, Industrial Temp(-40C ~85C) Bank Size -Bank1:8x8KB, 3x64KB -Bank2:28x64KB	3Q
					HY29DL162TF	70 90 120	Dual	Top Boot	10/10 10/10 10/10	0.2 0.2 0.2	1st Generation, Vcc: 2.7~3.6V, Industrial Temp(-40C ~85C) Bank Size -Bank1:8x8KB, 3x64KB -Bank2:28x64KB	3Q
					HY29DL163BF	70 90 120	Dual	Bottom Boot	10/10 10/10 10/10	0.2 0.2 0.2	1st Generation, Vcc: 2.7~3.6V, Industrial Temp(-40C ~85C) Bank Size -Bank1:8x8KB, 7x64KB -Bank2:24x64KB	2Q
					HY29DL163TF	70 90 120	Dual	Top Boot	10/10 10/10 10/10	0.2 0.2 0.2	1st Generation, Vcc: 2.7~3.6V, Industrial Temp(-40C ~85C) Bank Size -Bank1:8x8KB, 7x64KB -Bank2:24x64KB	Now
			48pin TSOP	2.0V	HY29DS162BT	120 130 140 150	Dual	Bottom Boot	5/5 5/5 5/5 5/5	0.065 0.065 0.065 0.065	1st Generation, Vcc: 2.7~3.6V, Industrial Temp(-40C ~85C) Bank Size -Bank1:8x8KB, 3x64KB -Bank2:28x64KB	3Q
					HY29DS162TT	120 130 140 150	Dual	Top Boot	5/5 5/5 5/5 5/5	0.065 0.065 0.065 0.065	1st Generation, Vcc: 2.7~3.6V, Industrial Temp(-40C ~85C) Bank Size -Bank1:8x8KB, 3x64KB -Bank2:28x64KB	3Q

FLASH MEMORY

TYPE	DENSITY	ORG.	PACKAGE	VOLT.	PART NUMBER	FEATURES					REMARKS	SAMPLE AVAILABLE
						SPEED (ns)	BANK	ARCHITECTURE (Sector type)	ICC(mA) BYTE/WORD	ISB1(uA)		
F L A S H	16M	2Mx8/ 1Mx16	48pin TSOP	2.0V	HY29DS163BT	120 130 140 150	Dual	Bottom Boot	5/5 5/5 5/5 5/5	0.065 0.065 0.065 0.065	1st Generation, Vcc: 2.7~3.6V, Industrial Temp(-40C ~85C) Bank Size -Bank1:8x8KB, 7x64KB -Bank2:24x64KB	Now
					HY29DS163TT	120 130 140 150	Dual	Top Boot	5/5 5/5 5/5 5/5	0.065 0.065 0.065 0.065	1st Generation, Vcc: 2.7~3.6V, Industrial Temp(-40C ~85C) Bank Size -Bank1:8x8KB, 7x64KB -Bank2:24x64KB	Now
			48pin FBGA	2.0V	HY29DS162BF	120 130 140 150	Dual	Bottom Boot	5/5 5/5 5/5 5/5	0.065 0.065 0.065 0.065	1st Generation, Vcc: 2.7~3.6V, Industrial Temp(-40C ~85C) Bank Size -Bank1:8x8KB, 3x64KB -Bank2:28x64KB	3Q
					HY29DS162TF	120 130 140 150	Dual	Top Boot	5/5 5/5 5/5 5/5	0.065 0.065 0.065 0.065	1st Generation, Vcc: 2.7~3.6V, Industrial Temp(-40C ~85C) Bank Size -Bank1:8x8KB, 3x64KB -Bank2:28x64KB	3Q
					HY29DS163BF	120 130 140 150	Dual	Bottom Boot	5/5 5/5 5/5 5/5	0.065 0.065 0.065 0.065	1st Generation, Vcc: 2.7~3.6V, Industrial Temp(-40C ~85C) Bank Size -Bank1:8x8KB, 7x64KB -Bank2:24x64KB	2Q
					HY29DS163TF	120 130 140 150	Dual	Top Boot	5/5 5/5 5/5 5/5	0.065 0.065 0.065 0.065	1st Generation, Vcc: 2.7~3.6V, Industrial Temp(-40C ~85C) Bank Size -Bank1:8x8KB, 7x64KB -Bank2:24x64KB	Now
	32M	4Mx8/ 2Mx16	48pin TSOP	2.0V	HY29DS322BT	100 110 120	Dual	Bottom Boot	5/5 5/5 5/5	1 1 1	1st Generation, Vcc: 1.8~2.2V, Bank Size -Bank1:8x8KB, 7x64KB -Bank2:56x64KB"	3Q
					HY29DS322TT	100 110 120	Dual	Top Boot	5/5 5/5 5/5	1 1 1	1st Generation, Vcc: 1.8~2.2V, Bank Size -Bank1:8x8KB, 7x64KB -Bank2:56x64KB"	3Q
					HY29DS323BT	100 110 120	Dual	Bottom Boot	5/5 5/5 5/5	1 1 1	1st Generation, Vcc: 1.8~2.2V, Bank Size -Bank1:8x8KB, 15x64KB -Bank2:48x64KB"	Now
					HY29DS323TT	100 110 120	Dual	Top Boot	5/5 5/5 5/5	1 1 1	1st Generation, Vcc: 1.8~2.2V, Bank Size -Bank1:8x8KB, 15x64KB -Bank2:48x64KB"	Now
			48pin FBGA	2.0V	HY29DS322BF	100 110 120	Dual	Bottom Boot	5/5 5/5 5/5	1 1 1	1st Generation, Vcc: 1.8~2.2V, Bank Size -Bank1:8x8KB, 7x64KB -Bank2:56x64KB	3Q
					HY29DS322TF	100 110 120	Dual	Top Boot	5/5 5/5 5/5	1 1 1	1st Generation, Vcc: 1.8~2.2V, Bank Size -Bank1:8x8KB, 7x64KB -Bank2:56x64KB	3Q
					HY29DS323BF	100 110 120	Dual	Bottom Boot	5/5 5/5 5/5	1 1 1	1st Generation, Vcc: 1.8~2.2V, Bank Size -Bank1:8x8KB, 15x64KB -Bank2:48x64KB"	2Q
					HY29DS323TF	100 110 120	Dual	Top Boot	5/5 5/5 5/5	1 1 1	1st Generation, Vcc: 1.8~2.2V, Bank Size -Bank1:8x8KB, 15x64KB -Bank2:48x64KB"	Now

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